

# Three Level ANPC Q2Pack Module

## NXH800A100L4Q2F2S1G/P1G, NXH800A100L4Q2F2S2G/P2G

This high-density, integrated power module combines high-performance IGBTs with rugged anti-parallel diodes.

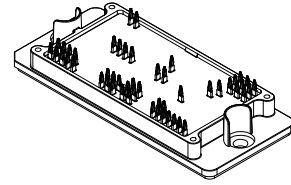
### Features

- Extremely Efficient Trench with Field Stop Technology
- Low Switching Loss Reduces System Power Dissipation
- Module Design Offers High Power Density
- Low Inductive Layout
- Low Package Height
- This is a Pb-Free Device

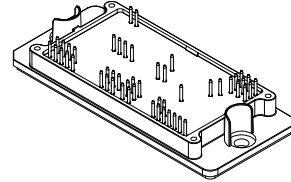
### Typical Applications

- Solar Inverters
- Uninterruptable Power Supplies Systems

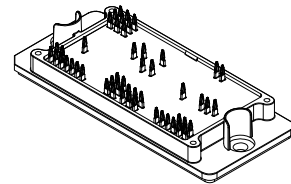
### PACKAGE PICTURE



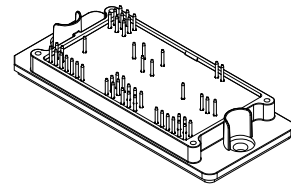
**Q2PACK POSITIVE PRESS FIT PINS  
 CASE 180HG**



**Q2PACK POSITIVE SOLDER PINS  
 CASE 180HH**



**Q2PACK NEGATIVE PRESS FIT PINS  
 CASE 180CQ**



**Q2PACK NEGATIVE SOLDER PINS  
 CASE 180BM**

### MARKING DIAGRAMS

See detailed marking diagrams on page 2 of this data sheet.

### PIN CONNECTIONS

See detailed pin connections on page 2 of this data sheet.

### ORDERING INFORMATION

See detailed ordering and shipping information on page 8 of this data sheet.

# NXH800A100L4Q2F2S1G/P1G, NXH800A100L4Q2F2S2G/P2G

## SCHEMATICS

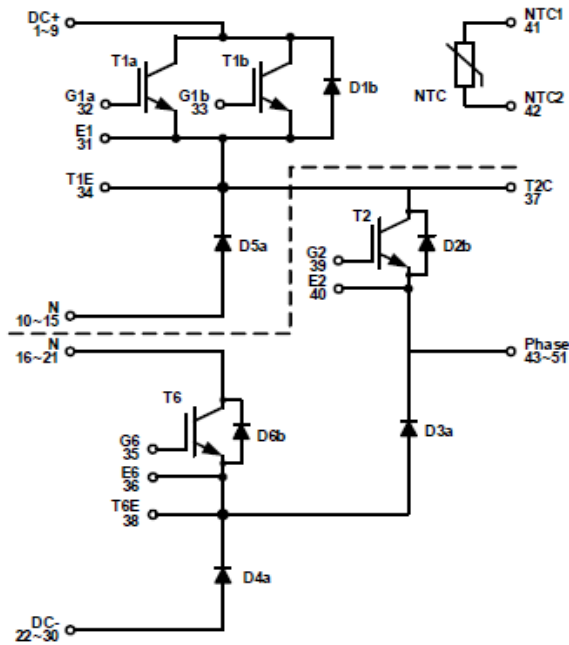


Figure 1. NXH800A100L4Q2F2X1G  
Schematic Diagram

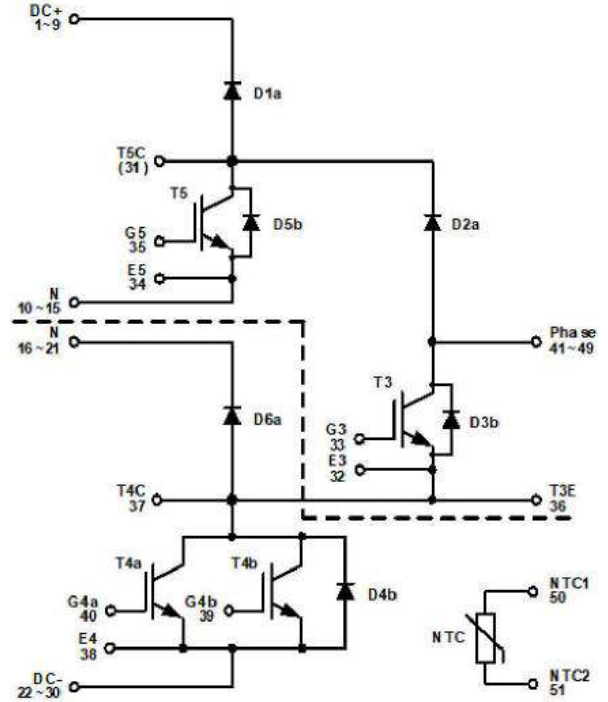
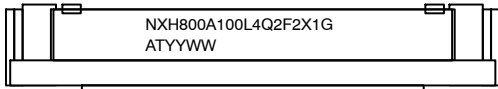


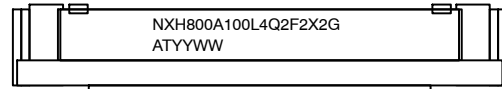
Figure 2. NXH800A100L4Q2F2X2G  
Schematic Diagram

## MARKING DIAGRAMS



NXH800A100L4Q2F2 = Specific Device Code  
X = P or S  
G = Pb-Free Package  
AT = Assembly & Test Site Code  
YYWW = Year and Work Week Code

Figure 3. NXH800A100L4Q2F2X1G  
Marking Diagram



NXH800A100L4Q2F2 = Specific Device Code  
X = P or S  
G = Pb-Free Package  
AT = Assembly & Test Site Code  
YYWW = Year and Work Week Code

Figure 4. NXH800A100L4Q2F2X2G  
Marking Diagram

## PIN CONNECTIONS

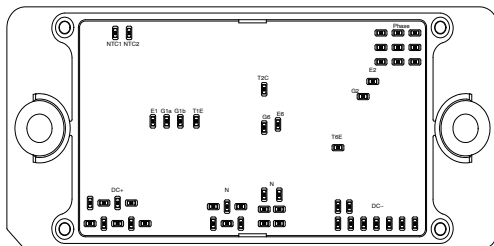


Figure 5. NXH800A100L4Q2F2X1G  
Pin Connection

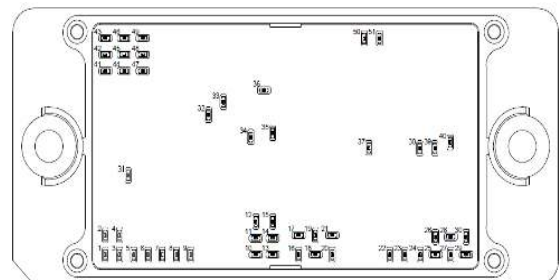


Figure 6. NXH800A100L4Q2F2X2G  
Pin Connection

# NXH800A100L4Q2F2S1G/P1G, NXH800A100L4Q2F2S2G/P2G

**Table 1. ABSOLUTE MAXIMUM RATINGS** ( $T_J = 25^\circ\text{C}$  unless otherwise noted)

Rating	Symbol	Value	Unit
<b>OUTER IGBT (T1a, T1b, T4a, T4b)</b>			
Collector-Emitter Voltage	$V_{CES}$	1000	V
Gate-Emitter Voltage Positive Transient Gate-Emitter Voltage ( $T_{pulse} = 5 \mu\text{s}$ , $D < 0.10$ )	$V_{GE}$	$\pm 20$ 30	V
Continuous Collector Current @ $T_C = 80^\circ\text{C}$	$I_C$	309	A
Pulsed Peak Collector Current @ $T_C = 80^\circ\text{C}$ ( $T_J = 175^\circ\text{C}$ )	$I_{C(Pulse)}$	927	A
Maximum Power Dissipation ( $T_J = 175^\circ\text{C}$ )	$P_{tot}$	714	W
Minimum Operating Junction Temperature	$T_{JMIN}$	-40	$^\circ\text{C}$
Maximum Operating Junction Temperature (Note 1)	$T_{JMAX}$	175	$^\circ\text{C}$
<b>INNER IGBT (T2, T3)</b>			
Collector-Emitter Voltage	$V_{CES}$	1000	V
Gate-Emitter Voltage Positive Transient Gate-Emitter Voltage ( $T_{pulse} = 5 \mu\text{s}$ , $D < 0.10$ )	$V_{GE}$	$\pm 20$ 30	V
Continuous Collector Current @ $T_C = 80^\circ\text{C}$	$I_C$	413	A
Pulsed Peak Collector Current @ $T_C = 80^\circ\text{C}$ ( $T_J = 175^\circ\text{C}$ )	$I_{C(Pulse)}$	1239	A
Maximum Power Dissipation ( $T_J = 175^\circ\text{C}$ )	$P_{tot}$	990	W
Minimum Operating Junction Temperature	$T_{JMIN}$	-40	$^\circ\text{C}$
Maximum Operating Junction Temperature (Note 1)	$T_{JMAX}$	175	$^\circ\text{C}$
<b>NEUTRAL POINT IGBT (T5, T6)</b>			
Collector-Emitter Voltage	$V_{CES}$	1000	V
Gate-Emitter Voltage Positive Transient Gate-Emitter Voltage ( $T_{pulse} = 5 \mu\text{s}$ , $D < 0.10$ )	$V_{GE}$	$\pm 20$ 30	V
Continuous Collector Current @ $T_C = 80^\circ\text{C}$	$I_C$	224	A
Pulsed Peak Collector Current @ $T_C = 80^\circ\text{C}$ ( $T_J = 175^\circ\text{C}$ )	$I_{C(Pulse)}$	672	A
Maximum Power Dissipation ( $T_J = 175^\circ\text{C}$ )	$P_{tot}$	543	W
Minimum Operating Junction Temperature	$T_{JMIN}$	-40	$^\circ\text{C}$
Maximum Operating Junction Temperature (Note 1)	$T_{JMAX}$	175	$^\circ\text{C}$
<b>IGBT INVERSE DIODE (D1b, D2b, D3b, D4b, D5b, D6b)</b>			
Peak Repetitive Reverse Voltage	$V_{RRM}$	1000	V
Continuous Forward Current @ $T_C = 80^\circ\text{C}$	$I_F$	61	A
Repetitive Peak Forward Current ( $T_J = 175^\circ\text{C}$ )	$I_{FRM}$	183	A
Maximum Power Dissipation ( $T_J = 175^\circ\text{C}$ )	$P_{tot}$	151	W
Minimum Operating Junction Temperature	$T_{JMIN}$	-40	$^\circ\text{C}$
Maximum Operating Junction Temperature	$T_{JMAX}$	175	$^\circ\text{C}$
<b>DIODES (D1a, D2a, D3a, D4a)</b>			
Peak Repetitive Reverse Voltage	$V_{RRM}$	1000	V
Continuous Forward Current @ $T_C = 80^\circ\text{C}$	$I_F$	177	A
Repetitive Peak Forward Current ( $T_J = 175^\circ\text{C}$ )	$I_{FRM}$	531	A
Maximum Power Dissipation ( $T_J = 175^\circ\text{C}$ )	$P_{tot}$	446	W
Minimum Operating Junction Temperature	$T_{JMIN}$	-40	$^\circ\text{C}$
Maximum Operating Junction Temperature	$T_{JMAX}$	175	$^\circ\text{C}$

## NXH800A100L4Q2F2S1G/P1G, NXH800A100L4Q2F2S2G/P2G

**Table 1. ABSOLUTE MAXIMUM RATINGS** ( $T_J = 25^\circ\text{C}$  unless otherwise noted) (continued)

Rating	Symbol	Value	Unit
<b>NEUTRAL POINT DIODES (D5a, D6a)</b>			
Peak Repetitive Reverse Voltage	$V_{RRM}$	1000	V
Continuous Forward Current @ $T_C = 80^\circ\text{C}$	$I_F$	238	A
Repetitive Peak Forward Current ( $T_J = 175^\circ\text{C}$ )	$I_{FRM}$	714	A
Maximum Power Dissipation ( $T_J = 175^\circ\text{C}$ )	$P_{tot}$	565	W
Minimum Operating Junction Temperature	$T_{JMIN}$	-40	$^\circ\text{C}$
Maximum Operating Junction Temperature	$T_{JMAX}$	175	$^\circ\text{C}$

**Table 2. THERMAL AND INSULATION PROPERTIES** ( $T_J = 25^\circ\text{C}$  unless otherwise noted)

Rating	Symbol	Value	Unit
<b>THERMAL PROPERTIES</b>			
Operating Temperature under Switching Condition	$T_{VJOP}$	-40 to +150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-40 to +125	$^\circ\text{C}$
<b>INSULATION PROPERTIES</b>			
Isolation Test Voltage, $t = 1$ s, 50 Hz	$V_{is}$	4000	$V_{RMS}$
Creepage Distance		12.7	mm
Comparative Tracking Index	CTI	> 600	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Refer to ELECTRICAL CHARACTERISTICS, RECOMMENDED OPERATING RANGES and/or APPLICATION INFORMATION for Safe Operating parameters.

# NXH800A100L4Q2F2S1G/P1G, NXH800A100L4Q2F2S2G/P2G

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise specified)

Characteristic	Test Conditions	Symbol	Min	Typ	Max	Unit
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### IGBT (T1a, T1b, T4a, T4b) CHARACTERISTICS

Collector-Emitter Cutoff Current	V <sub>GE</sub> = 0 V, V <sub>CE</sub> = 1000 V	I <sub>CES</sub>	–	–	20	μA	
Collector-Emitter Saturation Voltage	V <sub>GE</sub> = 15 V, I <sub>C</sub> = 400 A, T <sub>J</sub> = 25°C	V <sub>CE(sat)</sub>	–	1.69	2.3	V	
	V <sub>GE</sub> = 15 V, I <sub>C</sub> = 400 A, T <sub>J</sub> = 175°C		–	1.95	–		
Gate-Emitter Threshold Voltage	V <sub>GE</sub> = V <sub>CE</sub> , I <sub>C</sub> = 400 mA	V <sub>GE(TH)</sub>	3.4	4.92	6.7	V	
Gate Leakage Current	V <sub>GE</sub> = ±20 V, V <sub>CE</sub> = 0 V	I <sub>GES</sub>	–	–	±2	μA	
Turn-on Delay Time	T <sub>J</sub> = 25°C V <sub>CE</sub> = 600 V, I <sub>C</sub> = 200 A V <sub>GE</sub> = -9 V, 15 V R <sub>Goff</sub> = 23 Ω, R <sub>Gon</sub> = 15 Ω (T1a, T1b tested together)	t <sub>d(on)</sub>	–	189.93	–	ns	
Rise Time		t <sub>r</sub>	–	52.06	–		
Turn-off Delay Time		t <sub>d(off)</sub>	–	970.3	–		
Fall Time		t <sub>f</sub>	–	22.56	–		
Turn-on Switching Loss per Pulse		E <sub>on</sub>	–	7.71	–		mJ
Turn-off Switching Loss per Pulse		E <sub>off</sub>	–	8.12	–		
Turn-on Delay Time		T <sub>J</sub> = 125°C V <sub>CE</sub> = 600 V, I <sub>C</sub> = 200 A V <sub>GE</sub> = -9 V, 15 V R <sub>Goff</sub> = 23 Ω, R <sub>Gon</sub> = 15 Ω (T1a, T1b tested together)	t <sub>d(on)</sub>	–	164.22		–
Rise Time	t <sub>r</sub>		–	59.58	–		
Turn-off Delay Time	t <sub>d(off)</sub>		–	1088.34	–		
Fall Time	t <sub>f</sub>		–	33.6	–		
Turn-on Switching Loss per Pulse	E <sub>on</sub>		–	11.57	–	mJ	
Turn-off Switching Loss per Pulse	E <sub>off</sub>		–	10.77	–		
Input Capacitance	V <sub>CE</sub> = 20 V, V <sub>GE</sub> = 0 V, f = 100 kHz (T1a, T1b tested together)		C <sub>ies</sub>	–	49700	–	pF
Output Capacitance		C <sub>oes</sub>	–	1530	–		
Reverse Transfer Capacitance		C <sub>res</sub>	–	308	–		
Total Gate Charge	V <sub>CE</sub> = 600 V, I <sub>C</sub> = 300 A, V <sub>GE</sub> = -15 V~15 V (T1a, T1b tested together)	Q <sub>g</sub>	–	3040	–	nC	
Thermal Resistance – Chip-to-Heatsink	Thermal grease, Thickness = 2.1 Mil ±2% λ = 2.9 W/mK	R <sub>thJH</sub>	–	0.225	–	K/W	
Thermal Resistance – Chip-to-Case		R <sub>thJC</sub>	–	0.133	–	K/W	

### IGBT INVERSE DIODE (D1b, D2b, D3b, D4b, D5b, D6b) CHARACTERISTICS

Diode Forward Voltage	I <sub>F</sub> = 100 A, T <sub>J</sub> = 25°C	V <sub>F</sub>	–	2.73	3.7	V
	I <sub>F</sub> = 100 A, T <sub>J</sub> = 175°C		–	2.39	–	
Thermal Resistance – Chip-to-Heatsink	Thermal grease, Thickness = 2.1 Mil ±2% λ = 2.9 W/mK	R <sub>thJH</sub>	–	0.770	–	K/W
Thermal Resistance – Chip-to-Case		R <sub>thJC</sub>	–	0.63	–	K/W

# NXH800A100L4Q2F2S1G/P1G, NXH800A100L4Q2F2S2G/P2G

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise specified) (continued)

Characteristic	Test Conditions	Symbol	Min	Typ	Max	Unit	
<b>IGBT (T<sub>2</sub>, T<sub>3</sub>) CHARACTERISTICS</b>							
Collector-Emitter Cutoff Current	V <sub>GE</sub> = 0 V, V <sub>CE</sub> = 1000 V	I <sub>CES</sub>	–	–	20	μA	
Collector-Emitter Saturation Voltage	V <sub>GE</sub> = 15 V, I <sub>C</sub> = 600 A, T <sub>J</sub> = 25°C	V <sub>CE(sat)</sub>	–	1.75	2.3	V	
	V <sub>GE</sub> = 15 V, I <sub>C</sub> = 600 A, T <sub>J</sub> = 175°C		–	2.15	–		
Gate-Emitter Threshold Voltage	V <sub>GE</sub> = V <sub>CE</sub> , I <sub>C</sub> = 600 mA	V <sub>GE(TH)</sub>	3.4	4.83	6.7	V	
Gate Leakage Current	V <sub>GE</sub> = ±20 V, V <sub>CE</sub> = 0 V	I <sub>GES</sub>	–	–	±2	μA	
Turn-on Delay Time	T <sub>J</sub> = 25°C V <sub>CE</sub> = 600 V, I <sub>C</sub> = 200 A V <sub>GE</sub> = -9 V, 15 V R <sub>Gon</sub> = 11 Ω, R <sub>Goff</sub> = 23 Ω	t <sub>d(on)</sub>	–	233.73	–	ns	
Rise Time		t <sub>r</sub>	–	68	–		
Turn-off Delay Time		t <sub>d(off)</sub>	–	1364.18	–		
Fall Time		t <sub>f</sub>	–	79.12	–		
Turn-on Switching Loss per Pulse		E <sub>on</sub>	–	7.83	–		mJ
Turn-off Switching Loss per Pulse		E <sub>off</sub>	–	16.73	–		
Turn-on Delay Time	T <sub>J</sub> = 125°C V <sub>CE</sub> = 600 V, I <sub>C</sub> = 200 A V <sub>GE</sub> = -9 V, 15 V R <sub>Gon</sub> = 11 Ω, R <sub>Goff</sub> = 23 Ω	t <sub>d(on)</sub>	–	213.78	–	ns	
Rise Time		t <sub>r</sub>	–	75.99	–		
Turn-off Delay Time		t <sub>d(off)</sub>	–	1514.94	–		
Fall Time		t <sub>f</sub>	–	47.53	–		
Turn-on Switching Loss per Pulse		E <sub>on</sub>	–	10.87	–		mJ
Turn-off Switching Loss per Pulse		E <sub>off</sub>	–	17.39	–		
Input Capacitance	V <sub>CE</sub> = 20 V, V <sub>GE</sub> = 0 V, f = 100 kHz	C <sub>ies</sub>	–	38100	–	pF	
Output Capacitance		C <sub>oes</sub>	–	1230	–		
Reverse Transfer Capacitance		C <sub>res</sub>	–	226	–		
Total Gate Charge	V <sub>CE</sub> = 600 V, I <sub>C</sub> = 300 A, V <sub>GE</sub> = 15 V	Q <sub>g</sub>	–	2230	–	nC	
Thermal Resistance – Chip-to-Heatsink	Thermal grease, Thickness = 2.1 Mil ±2% λ = 2.9 W/mK	R <sub>thJH</sub>	–	0.168	–	K/W	
Thermal Resistance – Chip-to-Case		R <sub>thJC</sub>	–	0.096	–	K/W	

## DIODES (D1a, D2a, D3a, D4a) CHARACTERISTICS

Diode Forward Voltage	I <sub>F</sub> = 300 A, T <sub>J</sub> = 25°C	V <sub>F</sub>	–	2.76	3.7	V
	I <sub>F</sub> = 300 A, T <sub>J</sub> = 175°C		–	2.43	–	
Reverse Recovery Time	T <sub>J</sub> = 25°C V <sub>CE</sub> = 600 V, I <sub>C</sub> = 200 A V <sub>GE</sub> = -9 V, 15 V, R <sub>G</sub> = 11 Ω	t <sub>rr</sub>	–	105.26	–	ns
Reverse Recovery Charge		Q <sub>rr</sub>	–	4.344	–	μC
Peak Reverse Recovery Current		I <sub>RRM</sub>	–	106.04	–	A
Peak Rate of Fall of Recovery Current		di/dt	–	3.242	–	A/ns
Reverse Recovery Energy		E <sub>rr</sub>	–	1.304	–	mJ
Reverse Recovery Time		T <sub>J</sub> = 125°C V <sub>CE</sub> = 600 V, I <sub>C</sub> = 200 A V <sub>GE</sub> = -9 V, 15 V, R <sub>G</sub> = 11 Ω	t <sub>rr</sub>	–	176.9	–
Reverse Recovery Charge	Q <sub>rr</sub>		–	12.771	–	μC
Peak Reverse Recovery Current	I <sub>RRM</sub>		–	154.24	–	A
Peak Rate of Fall of Recovery Current	di/dt		–	2.795	–	A/ns
Reverse Recovery Energy	E <sub>rr</sub>		–	4.318	–	mJ
Thermal Resistance – Chip-to-Heatsink	Thermal grease, Thickness = 2.1 Mil ±2% λ = 2.9 W/mK		R <sub>thJH</sub>	–	0.315	–
Thermal Resistance – Chip-to-Case		R <sub>thJC</sub>	–	0.213	–	K/W

# NXH800A100L4Q2F2S1G/P1G, NXH800A100L4Q2F2S2G/P2G

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise specified) (continued)

Characteristic	Test Conditions	Symbol	Min	Typ	Max	Unit	
<b>IGBT (T5, T6) CHARACTERISTICS</b>							
Collector-Emitter Cutoff Current	V <sub>GE</sub> = 0 V, V <sub>CE</sub> = 1000 V	I <sub>CES</sub>	–	–	20	μA	
Collector-Emitter Saturation Voltage	V <sub>GE</sub> = 15 V, I <sub>C</sub> = 300 A, T <sub>J</sub> = 25°C	V <sub>CE(sat)</sub>	–	1.70	2.3	V	
	V <sub>GE</sub> = 15 V, I <sub>C</sub> = 300 A, T <sub>J</sub> = 175°C		–	2.05	–		
Gate-Emitter Threshold Voltage	V <sub>GE</sub> = V <sub>CE</sub> , I <sub>C</sub> = 300 mA	V <sub>GE(TH)</sub>	4.1	5.03	6.0	V	
Gate Leakage Current	V <sub>GE</sub> = ±20 V, V <sub>CE</sub> = 0 V	I <sub>GES</sub>	–	–	±2	μA	
Turn-on Delay Time	T <sub>J</sub> = 25°C V <sub>CE</sub> = 600 V, I <sub>C</sub> = 200 A V <sub>GE</sub> = -9 V, 15 V, R <sub>Gon</sub> = 11 Ω, R <sub>Goff</sub> = 23 Ω	t <sub>d(on)</sub>	–	120.19	–	ns	
Rise Time		t <sub>r</sub>	–	50.18	–		
Turn-off Delay Time		t <sub>d(off)</sub>	–	682.65	–		
Fall Time		t <sub>f</sub>	–	39.56	–		
Turn-on Switching Loss per Pulse		E <sub>on</sub>	–	8.58	–		mJ
Turn-off Switching Loss per Pulse		E <sub>off</sub>	–	7.82	–		
Turn-on Delay Time		T <sub>J</sub> = 125°C V <sub>CE</sub> = 600 V, I <sub>C</sub> = 200 A V <sub>GE</sub> = -9 V, 15 V, R <sub>Gon</sub> = 11 Ω, R <sub>Goff</sub> = 23 Ω	t <sub>d(on)</sub>	–	112.48		–
Rise Time	t <sub>r</sub>		–	57.46	–		
Turn-off Delay Time	t <sub>d(off)</sub>		–	747.87	–		
Fall Time	t <sub>f</sub>		–	23.765	–		
Turn-on Switching Loss per Pulse	E <sub>on</sub>		–	13.77	–	mJ	
Turn-off Switching Loss per Pulse	E <sub>off</sub>		–	10.41	–		
Input Capacitance	V <sub>CE</sub> = 20 V, V <sub>GE</sub> = 0 V, f = 100 kHz		C <sub>ies</sub>	–	17400	–	pF
Output Capacitance		C <sub>oes</sub>	–	654	–		
Reverse Transfer Capacitance		C <sub>res</sub>	–	101	–		
Total Gate Charge	V <sub>CE</sub> = 600 V, I <sub>C</sub> = 300 A, V <sub>GE</sub> = 15 V	Q <sub>g</sub>	–	1004	–	nC	
Thermal Resistance – Chip-to-Heatsink	Thermal grease, Thickness = 2.1 Mil ±2% λ = 2.9 W/mK	R <sub>thJH</sub>	–	0.264	–	K/W	
Thermal Resistance – Chip-to-Case		R <sub>thJC</sub>	–	0.175	–	K/W	

## DIODES (D5a, D6a) CHARACTERISTICS

Diode Forward Voltage	I <sub>F</sub> = 400 A, T <sub>J</sub> = 25°C	V <sub>F</sub>	–	2.83	3.7	V	
	I <sub>F</sub> = 400 A, T <sub>J</sub> = 175°C		–	2.42	–		
Reverse Recovery Time	T <sub>J</sub> = 25°C V <sub>CE</sub> = 600 V, I <sub>C</sub> = 200 A V <sub>GE</sub> = -9 V, 15 V, R <sub>G</sub> = 15 Ω	t <sub>rr</sub>	–	92.74	–	ns	
Reverse Recovery Charge		Q <sub>rr</sub>	–	5.66	–	μC	
Peak Reverse Recovery Current		I <sub>RRM</sub>	–	136.18	–	A	
Peak Rate of Fall of Recovery Current		di/dt	–	3.14	–	A/ns	
Reverse Recovery Energy		E <sub>rr</sub>	–	2.03	–	mJ	
Reverse Recovery Time		T <sub>J</sub> = 125°C V <sub>CE</sub> = 600 V, I <sub>C</sub> = 200 A V <sub>GE</sub> = -9 V, 15 V, R <sub>G</sub> = 15 Ω	t <sub>rr</sub>	–	159.63	–	ns
Reverse Recovery Charge			Q <sub>rr</sub>	–	17.00	–	μC
Peak Reverse Recovery Current	I <sub>RRM</sub>		–	223.97	–	A	
Peak Rate of Fall of Recovery Current	di/dt		–	2.71	–	A/ns	
Reverse Recovery Energy	E <sub>rr</sub>		–	6.80	–	mJ	
Thermal Resistance – Chip-to-Heatsink	Thermal grease, Thickness = 2.1 Mil ±2% λ = 2.9 W/mK		R <sub>thJH</sub>	–	0.244	–	K/W
Thermal Resistance – Chip-to-Case		R <sub>thJC</sub>	–	0.168	–	K/W	

## NXH800A100L4Q2F2S1G/P1G, NXH800A100L4Q2F2S2G/P2G

### ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise specified) (continued)

Characteristic	Test Conditions	Symbol	Min	Typ	Max	Unit
<b>THERMISTOR CHARACTERISTICS</b>						
Nominal Resistance	T = 25°C	R <sub>25</sub>	–	22	–	kΩ
Nominal Resistance	T = 100°C	R <sub>100</sub>	–	1504	–	Ω
Deviation of R25		ΔR/R	–1	–	1	%
Power Dissipation		P <sub>D</sub>	–	187.5	–	mW
Power Dissipation Constant			–	1.5	–	mW/K
B-value	B(25/100), tolerance ±3%		–	3980	–	K

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

### ORDERING INFORMATION

Part Number	Marking	Package	Shipping
NXH800A100L4Q2F2S1G	NXH800A100L4Q2F2S1G	Q2PACK – Case 180HH (Pb-Free/Halide-Free)	12 Units / Blister Tray
NXH800A100L4Q2F2P1G	NXH800A100L4Q2F2P1G	Q2PACK – Case 180HG (Pb-Free/Halide-Free)	12 Units / Blister Tray
NXH800A100L4Q2F2S2G	NXH800A100L4Q2F2S2G	Q2PACK – Case 180BM (Pb-Free/Halide-Free)	12 Units / Blister Tray
NXH800A100L4Q2F2P2G	NXH800A100L4Q2F2P2G	Q2PACK – Case 180CQ (Pb-Free/Halide-Free)	12 Units / Blister Tray



# NXH800A100L4Q2F2S1G/P1G, NXH800A100L4Q2F2S2G/P2G

## TYPICAL CHARACTERISTICS – IGBT T1/T4 AND D5a/D6a DIODE

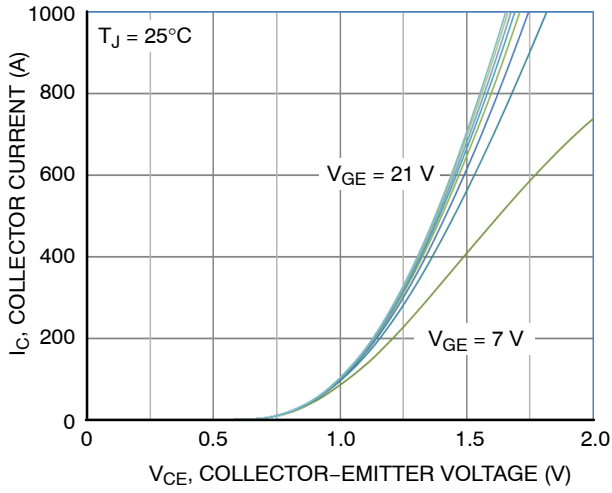


Figure 7. Typical Output Characteristics

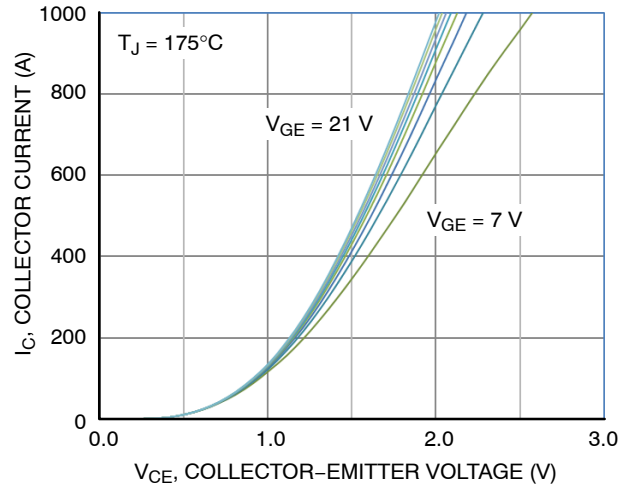


Figure 8. Typical Output Characteristics

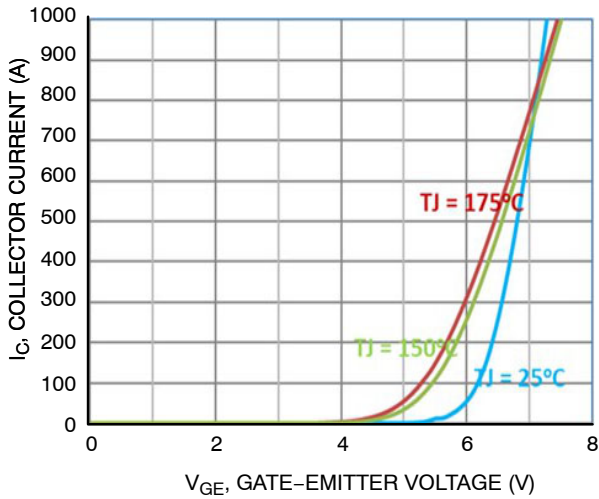


Figure 9. Transfer Characteristics

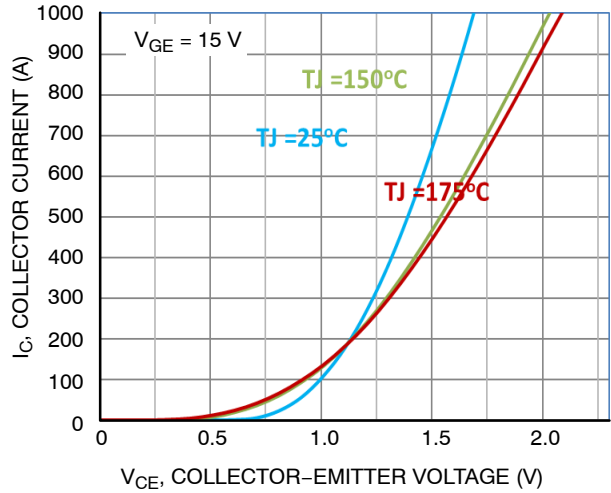


Figure 10. Saturation Voltage Characteristics

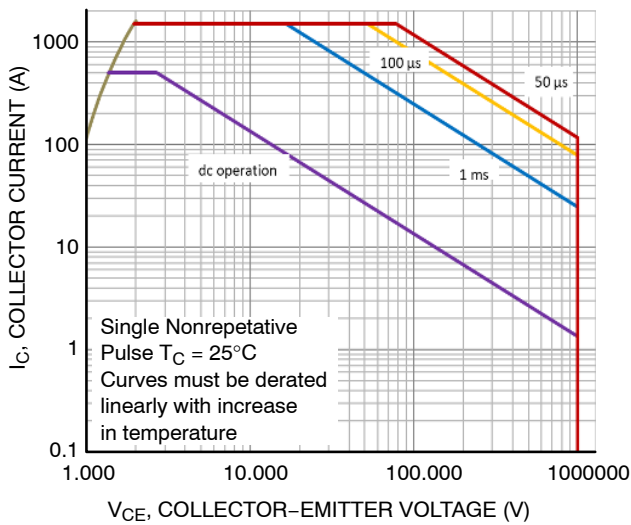


Figure 11. FBSOA

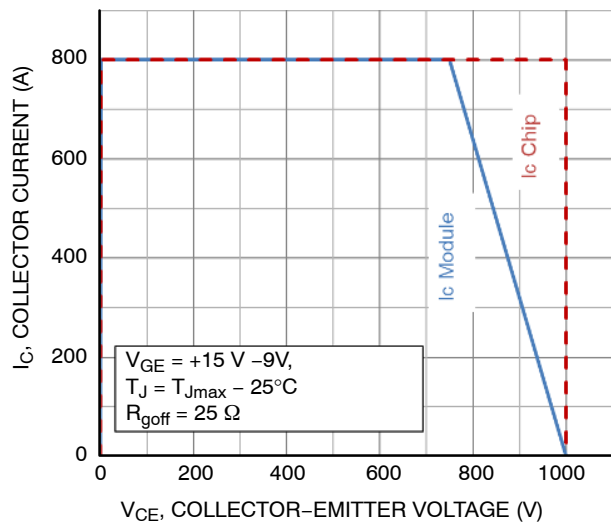
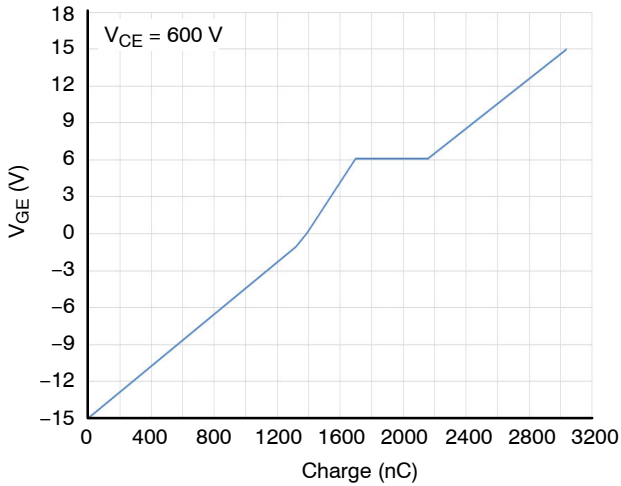


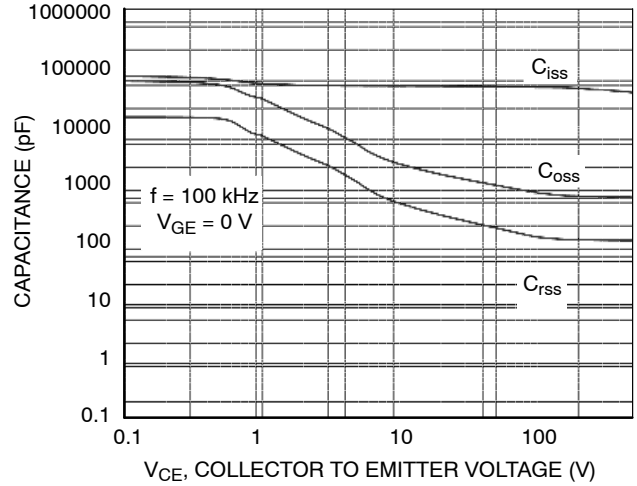
Figure 12. RBSOA

# NXH800A100L4Q2F2S1G/P1G, NXH800A100L4Q2F2S2G/P2G

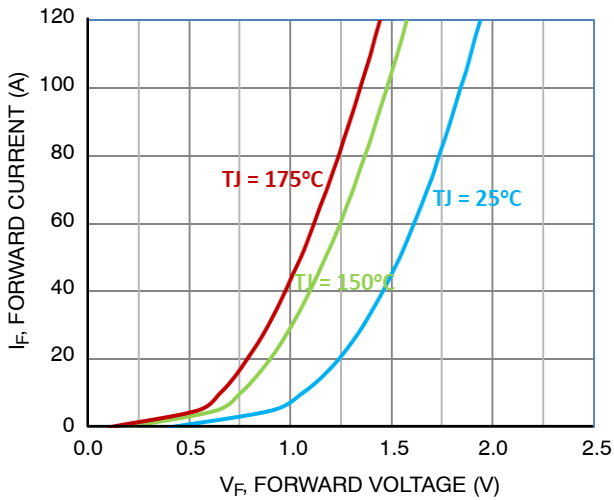
## TYPICAL CHARACTERISTICS – IGBT T1/T4 AND D5a/D6a DIODE (continued)



**Figure 13. Gate Voltage vs. Gate Charge (T1a + T1b)**

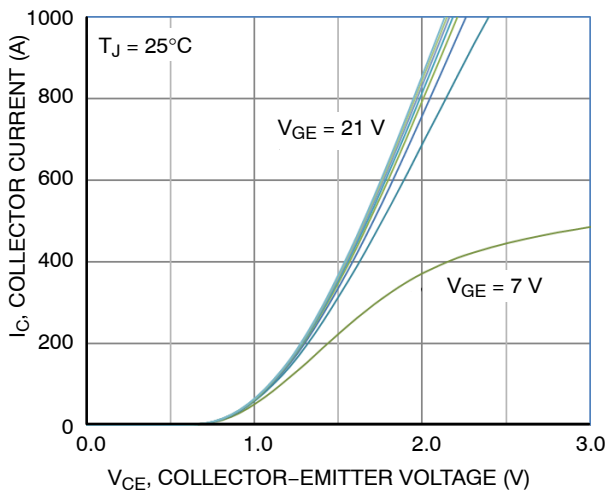


**Figure 14. Capacitance (T1, T4)**

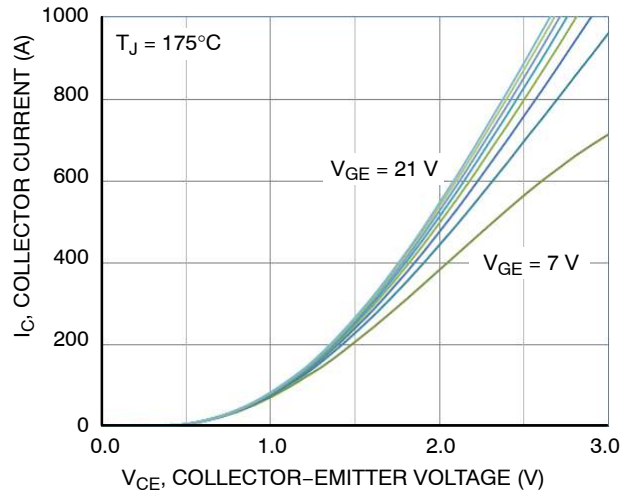


**Figure 15. Diode Forward Characteristics**

## TYPICAL CHARACTERISTICS – IGBT T2/T3 AND D1a/D4a, D2a/D3a DIODE



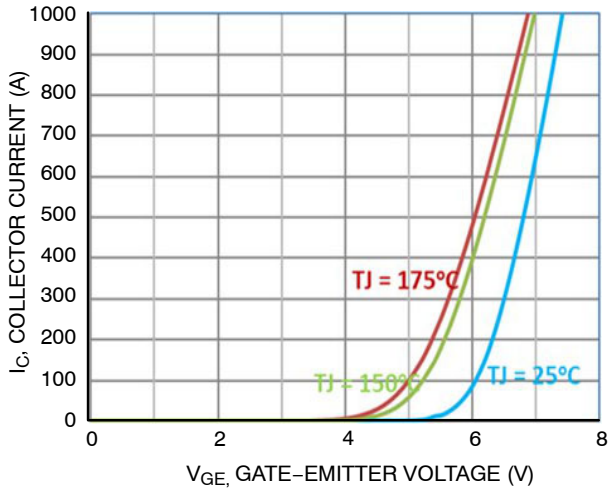
**Figure 16. Typical Output Characteristics**



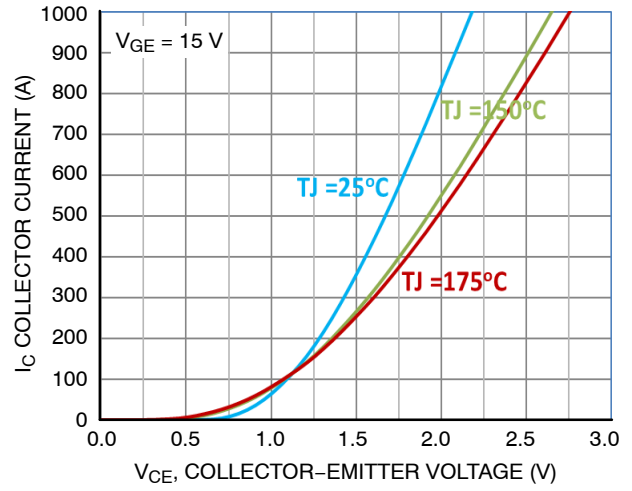
**Figure 17. Typical Output Characteristics**

# NXH800A100L4Q2F2S1G/P1G, NXH800A100L4Q2F2S2G/P2G

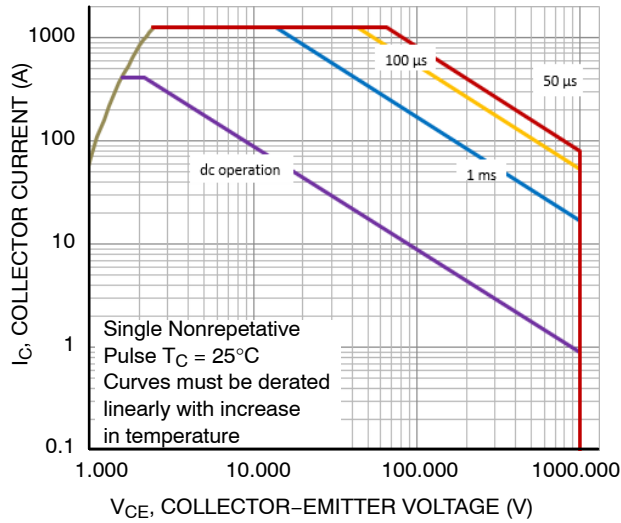
## TYPICAL CHARACTERISTICS – IGBT T2/T3 AND D1a/D4a, D2a/D3a DIODE (continued)



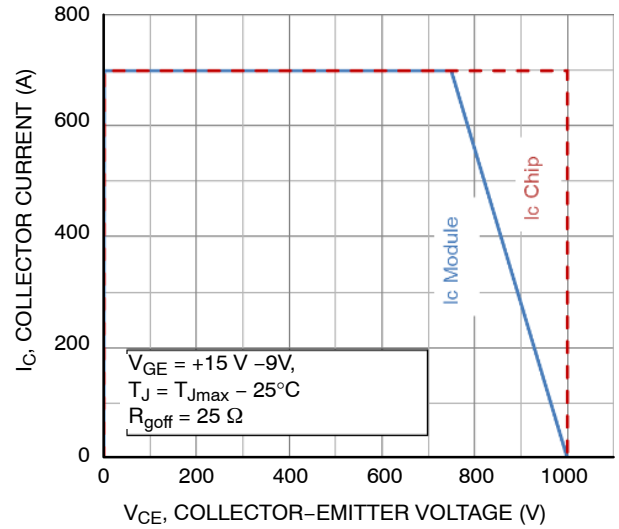
**Figure 18. Transfer Characteristics**



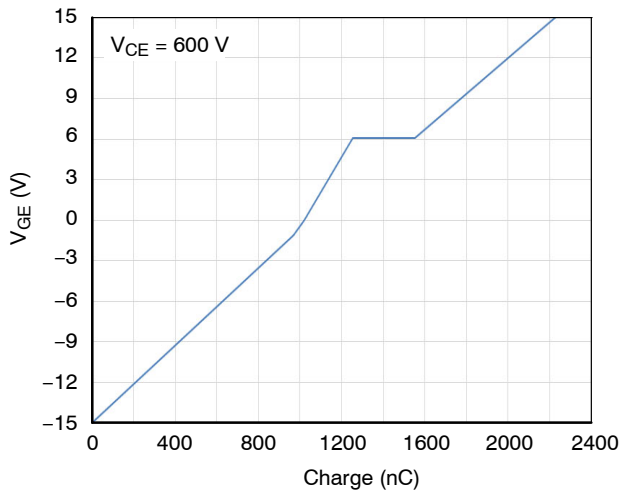
**Figure 19. Saturation Voltage Characteristic**



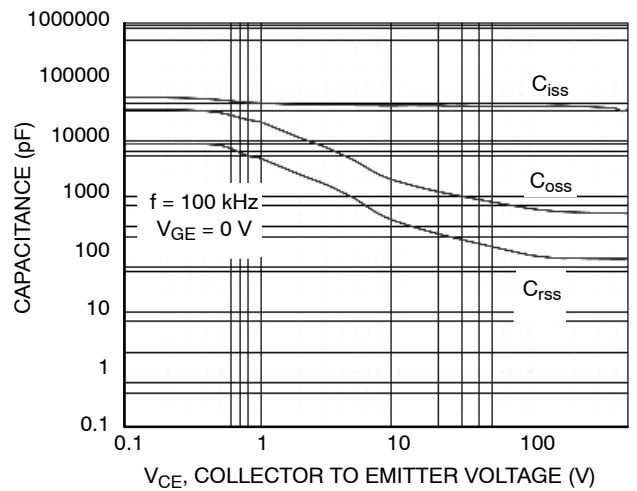
**Figure 20. FBSOA**



**Figure 21. RBSOA**



**Figure 22. Gate Voltage vs. Gate Charge**



**Figure 23. Capacitance**

# NXH800A100L4Q2F2S1G/P1G, NXH800A100L4Q2F2S2G/P2G

## TYPICAL CHARACTERISTICS – IGBT T2/T3 AND D1a/D4a, D2a/D3a DIODE (continued)

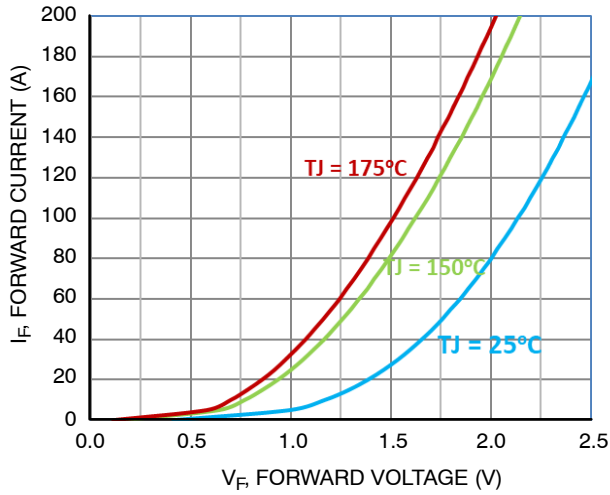


Figure 24. Diode Forward Characteristics

## TYPICAL CHARACTERISTICS – IGBT T5/T6 AND D1b/D2b/D6b, D3b/D4b/D5b DIODE (continued)

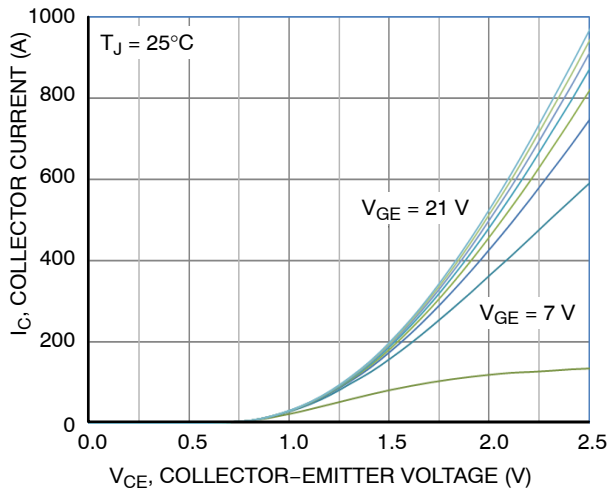


Figure 25. Typical Output Characteristics

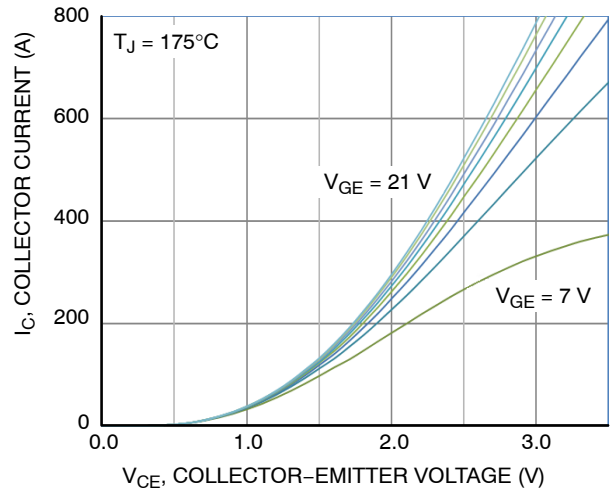
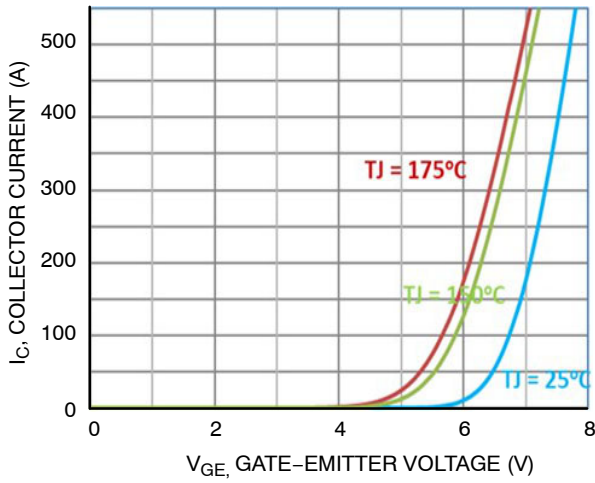


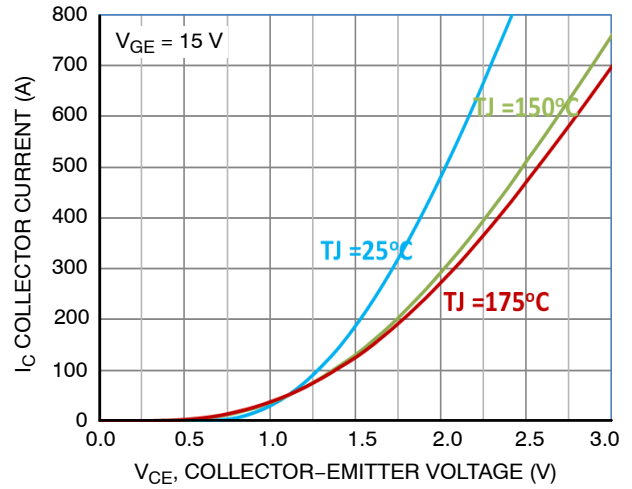
Figure 26. Typical Output Characteristics

# NXH800A100L4Q2F2S1G/P1G, NXH800A100L4Q2F2S2G/P2G

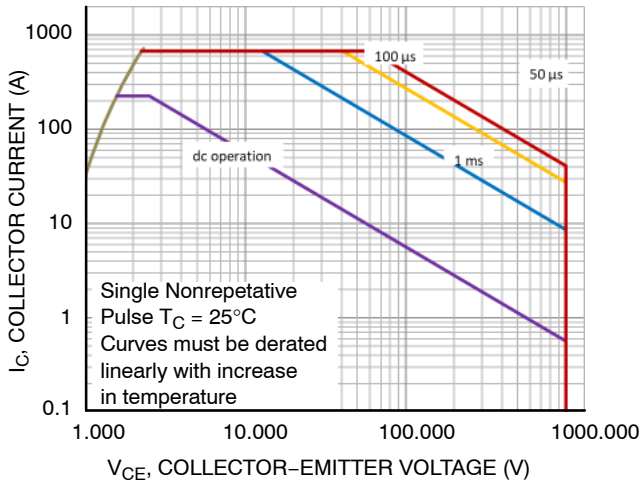
## TYPICAL CHARACTERISTICS – IGBT T5/T6 AND D1b/D2b/D6b, D3b/D4b/D5b DIODE (continued)



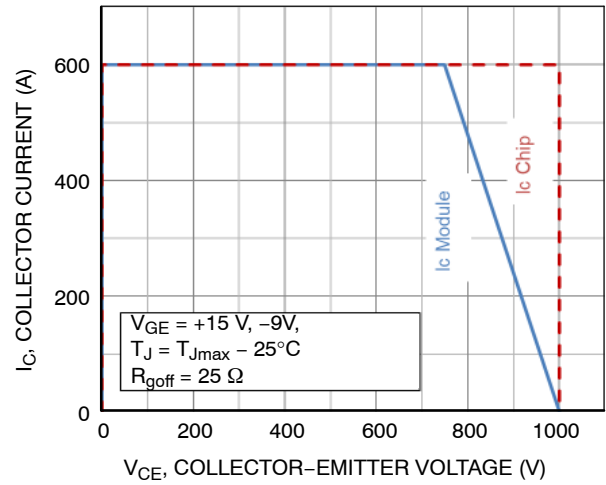
**Figure 27. Transfer Characteristics**



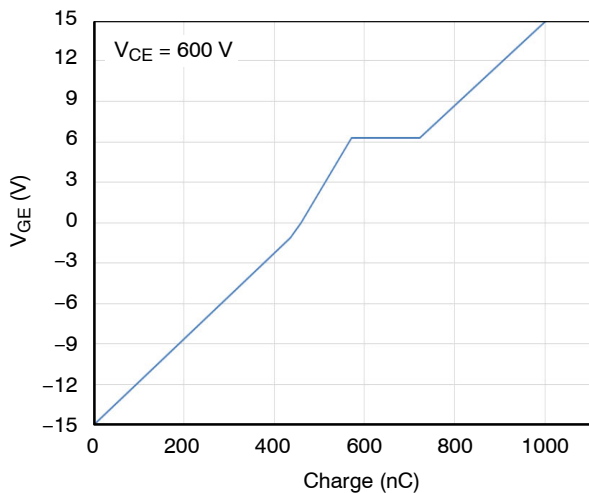
**Figure 28. Saturation Voltage Characteristic**



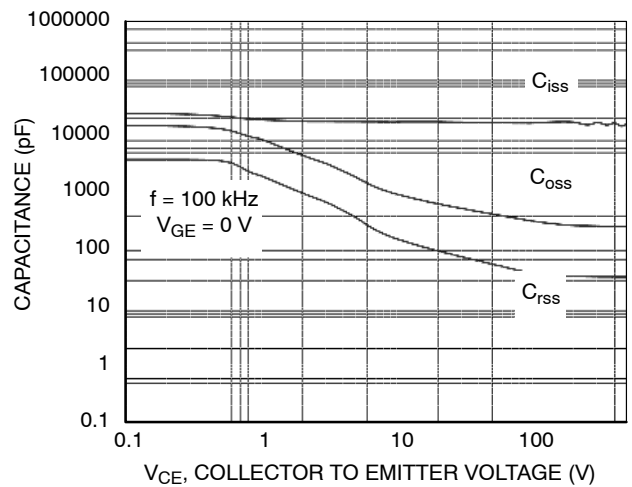
**Figure 29. FBSOA**



**Figure 30. RBSOA**



**Figure 31. Gate Voltage vs. Gate Charge**



**Figure 32. Capacitance**

# NXH800A100L4Q2F2S1G/P1G, NXH800A100L4Q2F2S2G/P2G

## TYPICAL CHARACTERISTICS – IGBT T5/T6 AND D1b/D2b/D6b, D3b/D4b/D5b DIODE (continued)

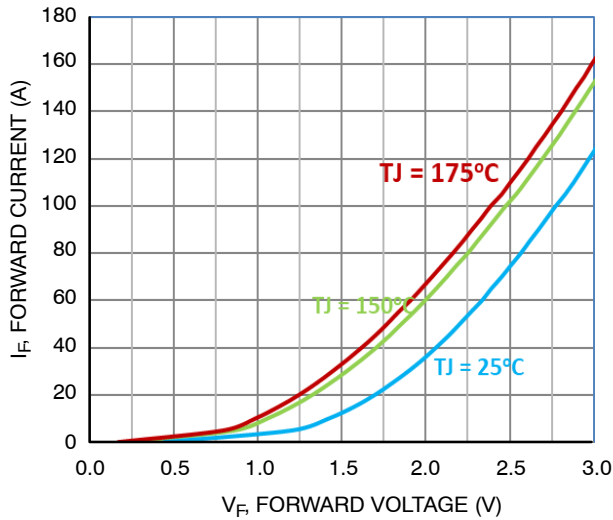


Figure 33. Diode Forward Characteristics

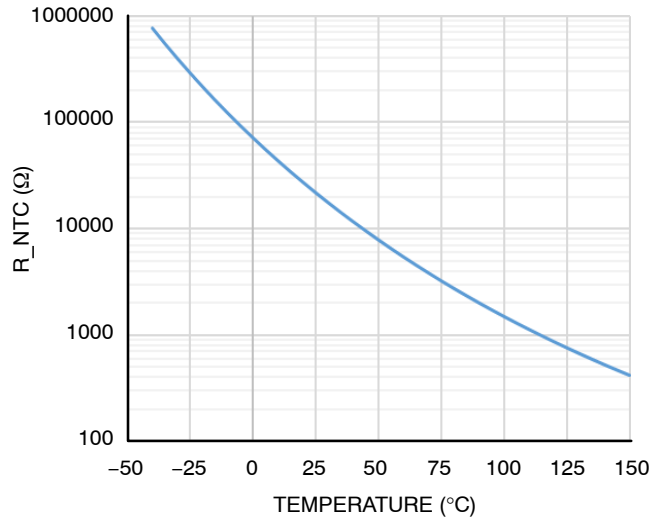


Figure 34. Temperature vs. NTC Value

## TYPICAL CHARACTERISTICS – IGBT AND DIODE

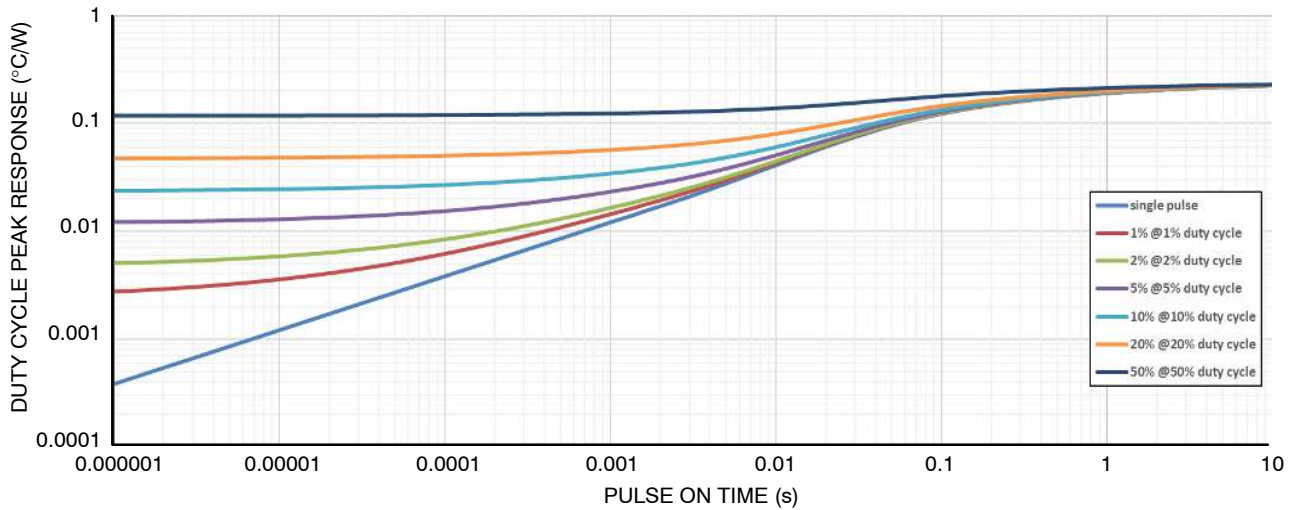


Figure 35. Transient Thermal Impedance (T1a, T1b, T4a, T4b)

TYPICAL CHARACTERISTICS – IGBT AND DIODE (continued)

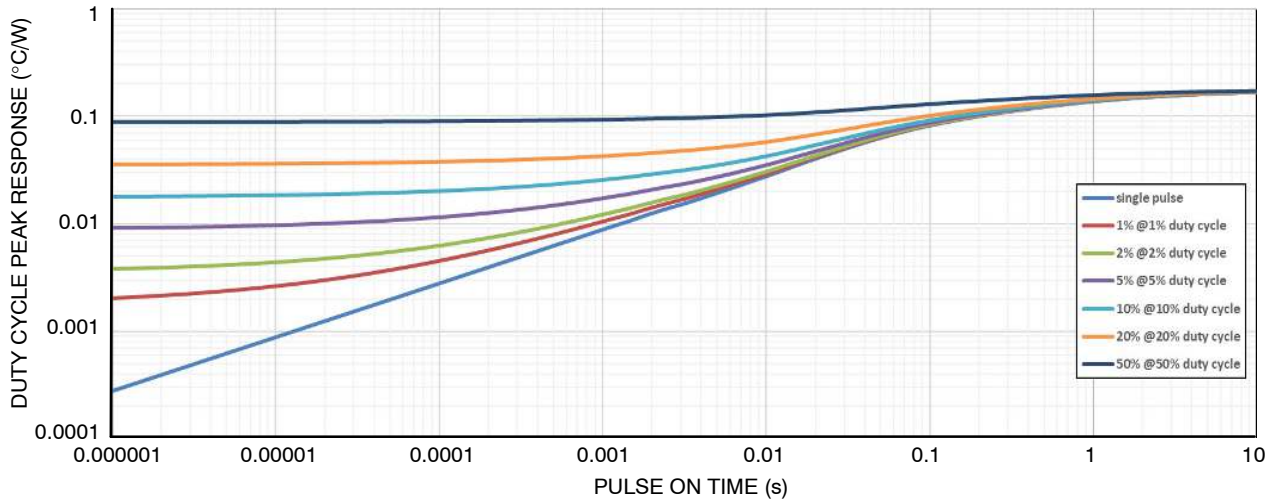


Figure 36. Transient Thermal Impedance (T2, T3)

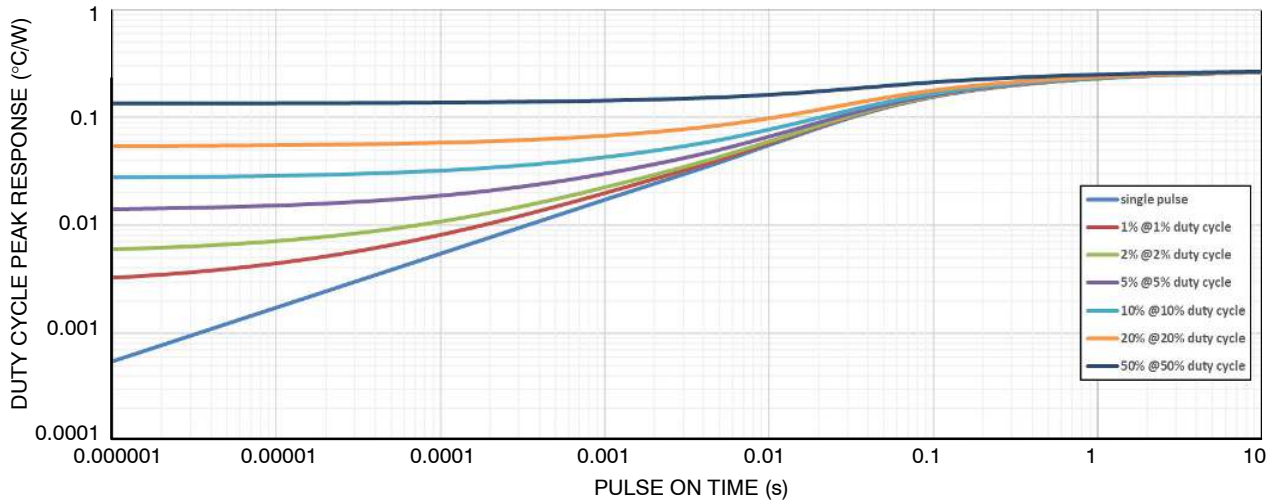


Figure 37. Transient Thermal Impedance (T5, T6)

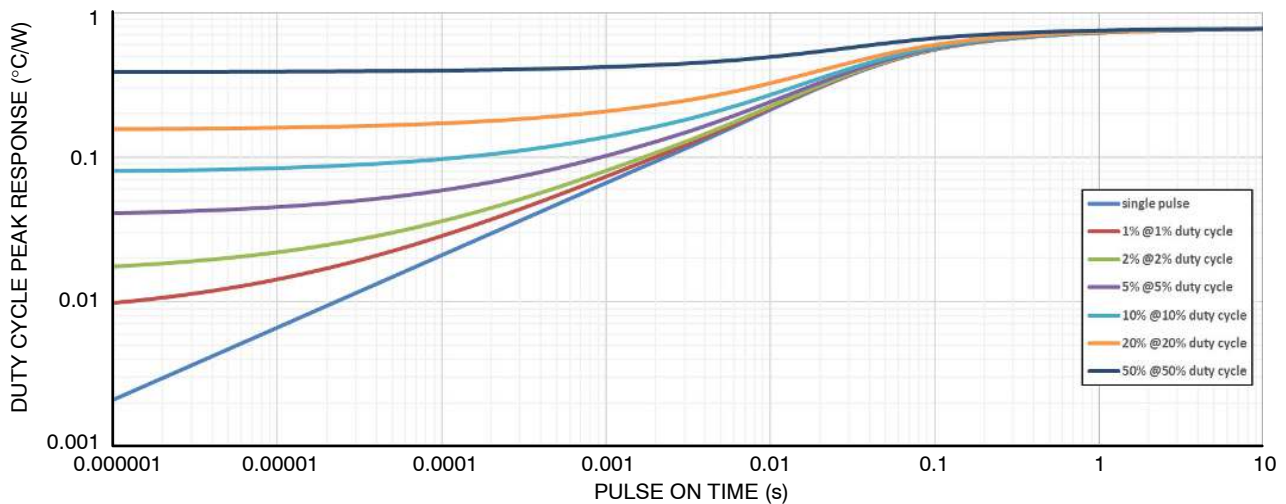


Figure 38. Transient Thermal Impedance (D1b, D2b, D3b, D4b, D5b, D6b)

# NXH800A100L4Q2F2S1G/P1G, NXH800A100L4Q2F2S2G/P2G

## TYPICAL CHARACTERISTICS – IGBT AND DIODE (continued)

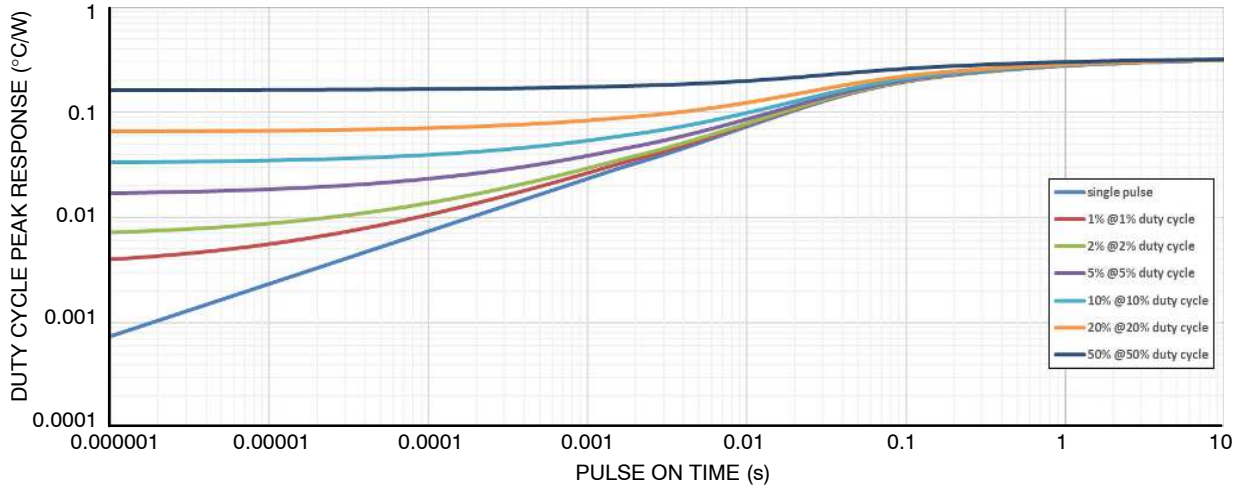


Figure 39. Transient Thermal Impedance (D1a, D2a, D3a, D4a)

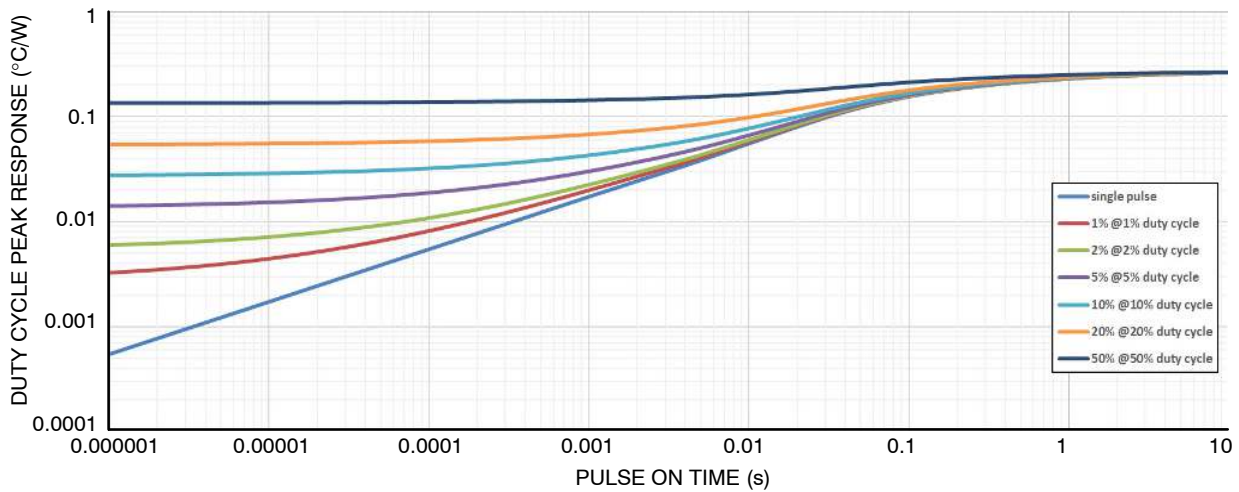


Figure 40. Transient Thermal Impedance (D5a, D6a)

## TYPICAL CHARACTERISTICS – T1||D5a or T4||D6a

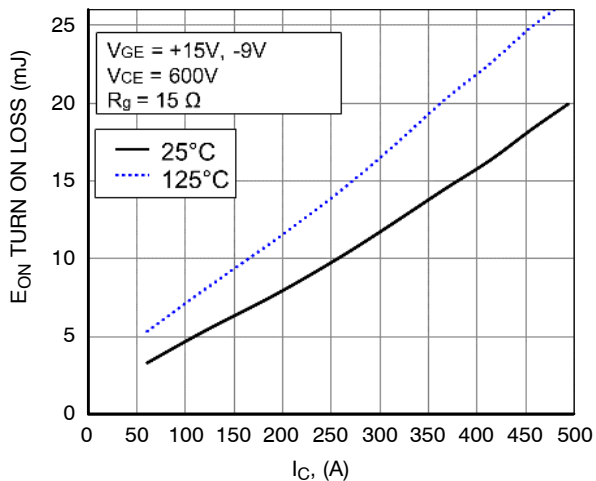


Figure 41. Typical Turn On Loss vs.  $I_C$

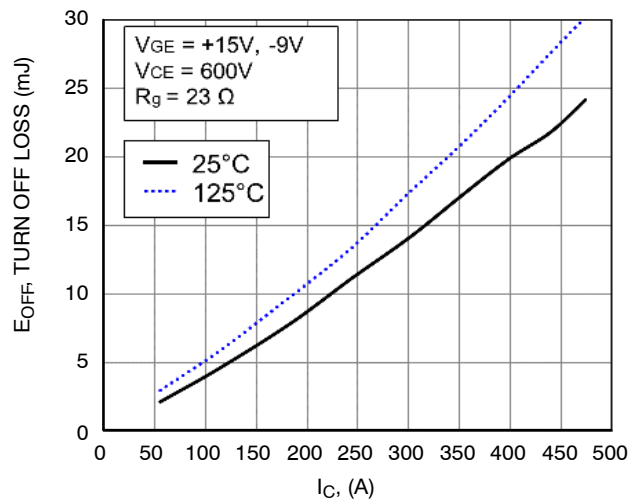
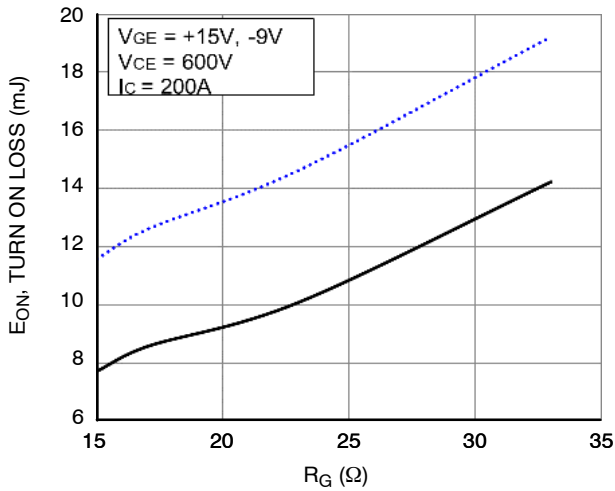


Figure 42. Typical Turn Off Loss vs.  $I_C$

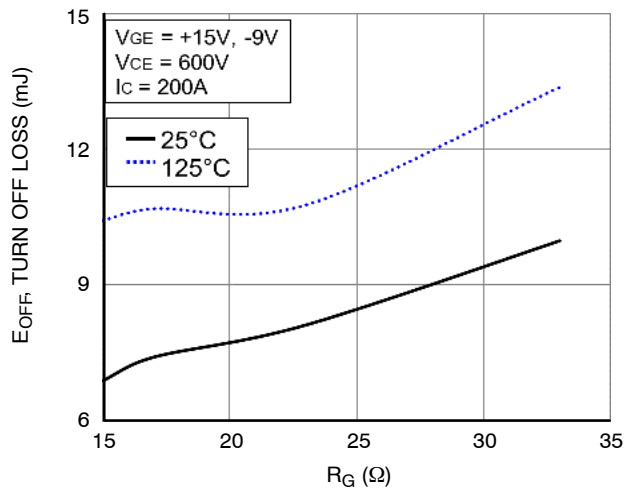


# NXH800A100L4Q2F2S1G/P1G, NXH800A100L4Q2F2S2G/P2G

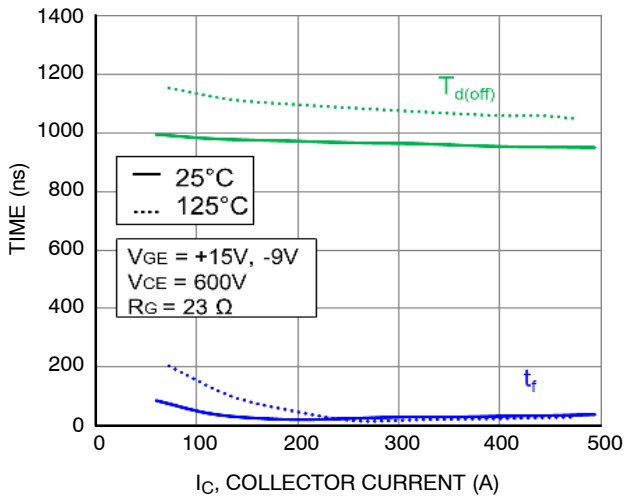
## TYPICAL CHARACTERISTICS – T1||D5a or T4||D6a (continued)



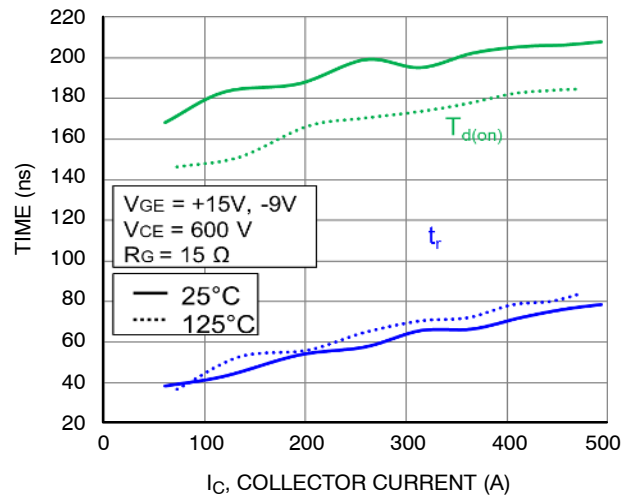
**Figure 43. Typical Turn On Loss vs.  $R_G$**



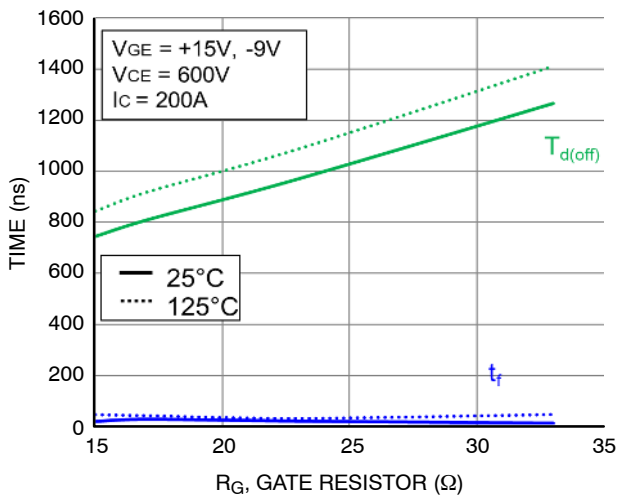
**Figure 44. Typical Turn Off Loss vs.  $R_G$**



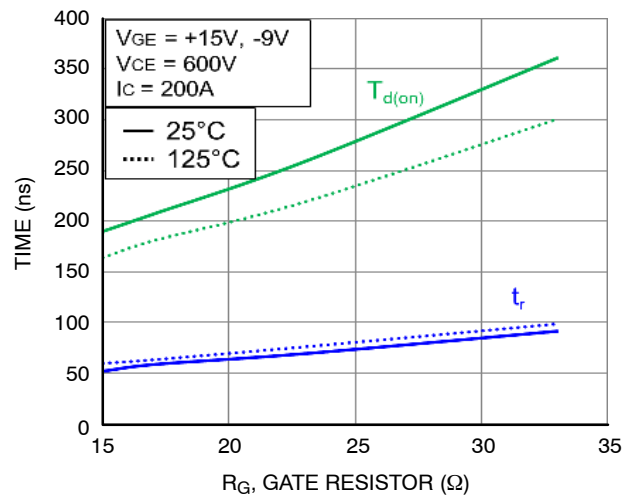
**Figure 45. Typical Turn-Off Switching Time vs.  $I_C$**



**Figure 46. Typical Turn-On Switching Time vs.  $I_C$**



**Figure 47. Typical Turn-Off Switching Time vs.  $R_G$**



**Figure 48. Typical Turn-On Switching Time vs.  $R_G$**

# NXH800A100L4Q2F2S1G/P1G, NXH800A100L4Q2F2S2G/P2G

## TYPICAL CHARACTERISTICS – T1||D5a or T4||D6a (continued)

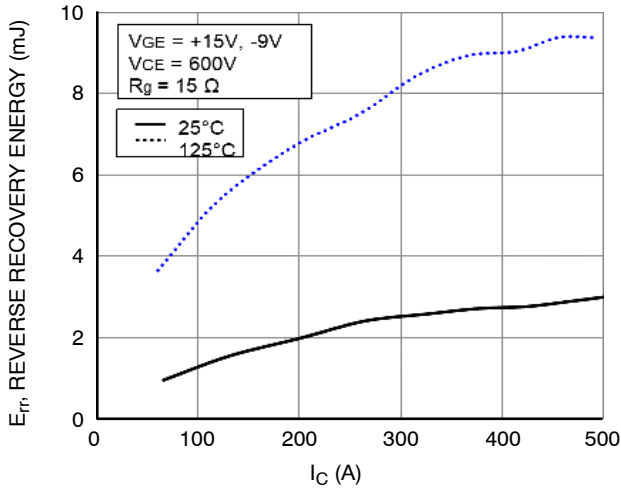


Figure 49. Typical Reverse Recovery Energy Loss vs.  $I_C$

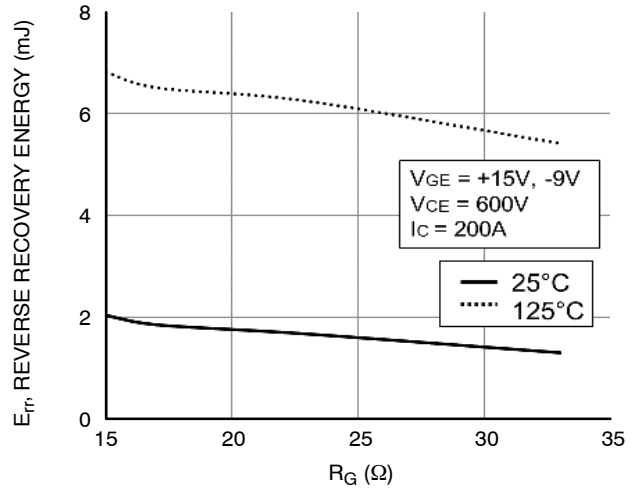


Figure 50. Typical Reverse Recovery Energy Loss vs.  $R_G$

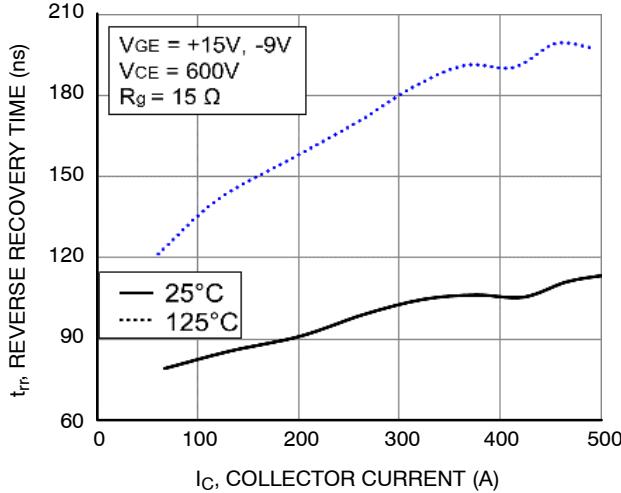


Figure 51. Typical Reverse Recovery Time vs.  $I_C$

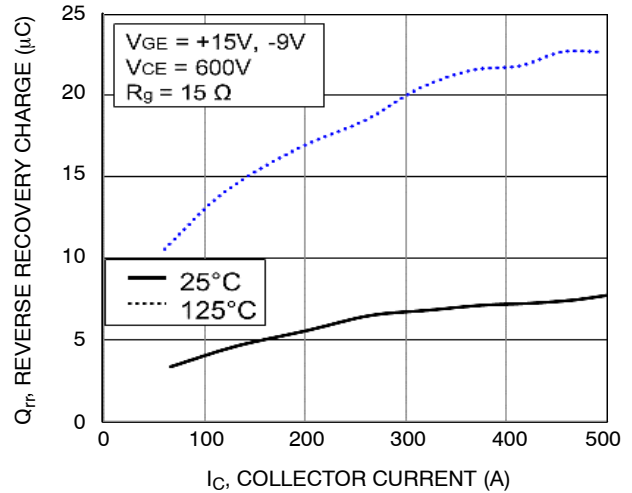


Figure 52. Typical Reverse Recovery Charge vs.  $I_C$

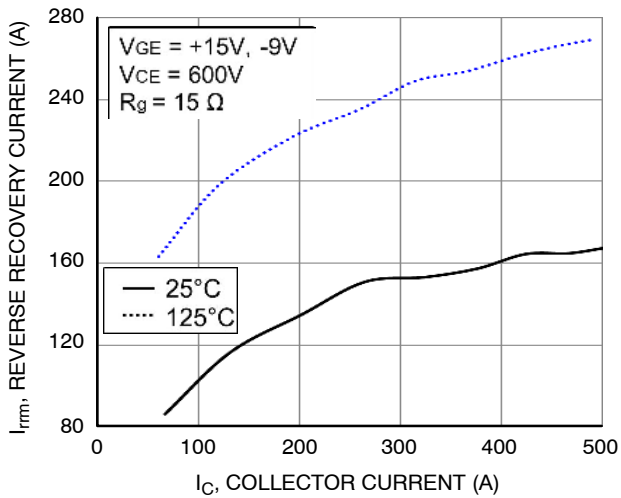


Figure 53. Typical Reverse Recovery Current vs.  $I_C$

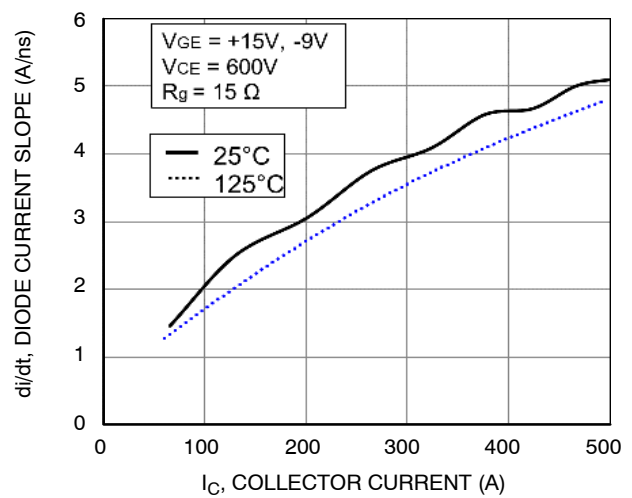


Figure 54. Typical  $di/dt$  vs.  $I_C$

# NXH800A100L4Q2F2S1G/P1G, NXH800A100L4Q2F2S2G/P2G

## TYPICAL CHARACTERISTICS – T1||D5a or T4||D6a (continued)

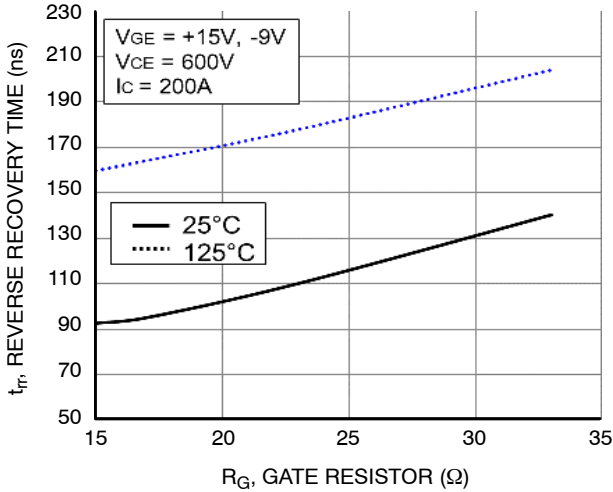


Figure 55. Typical Reverse Recovery Time vs.  $R_G$

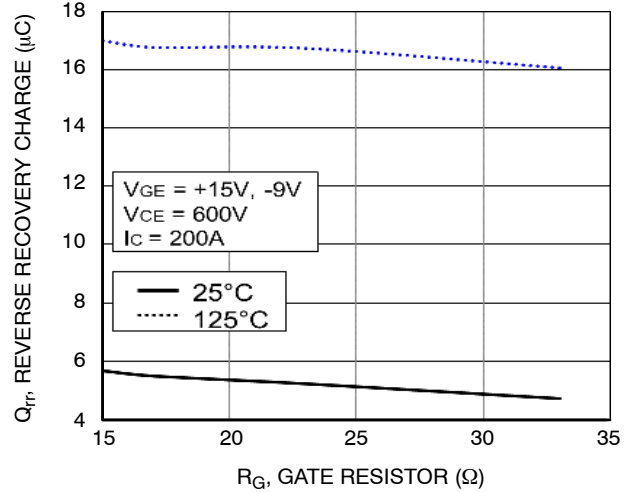


Figure 56. Typical Reverse Recovery Charge vs.  $R_G$

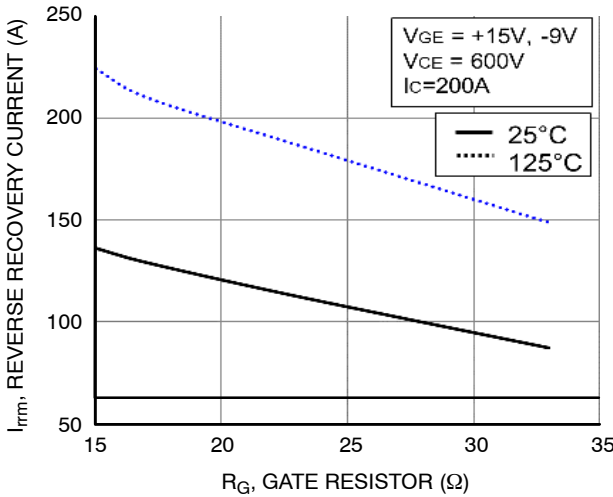


Figure 57. Typical Reverse Recovery Peak Current vs.  $R_G$

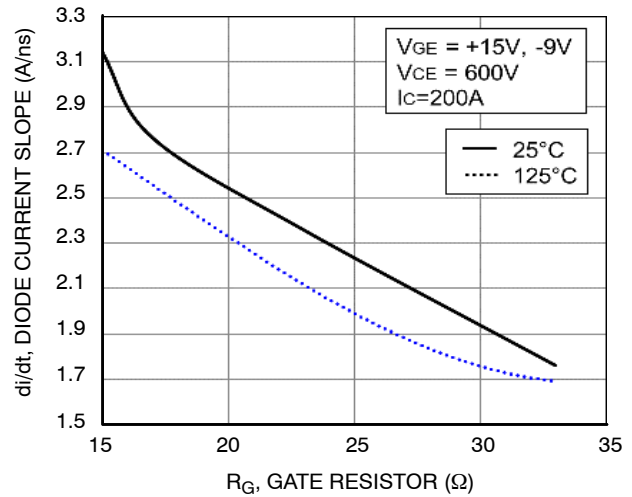


Figure 58. Typical  $di/dt$  vs.  $R_G$

## TYPICAL CHARACTERISTICS – T2||D3a + D4a or T3||D1a + D2a

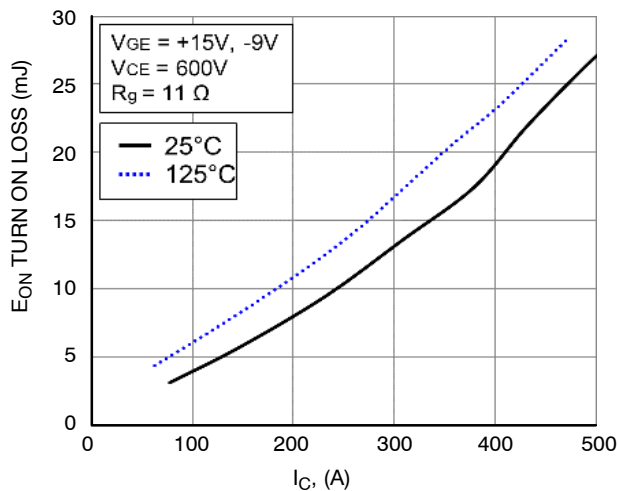


Figure 59. Typical Turn On Loss vs.  $I_C$

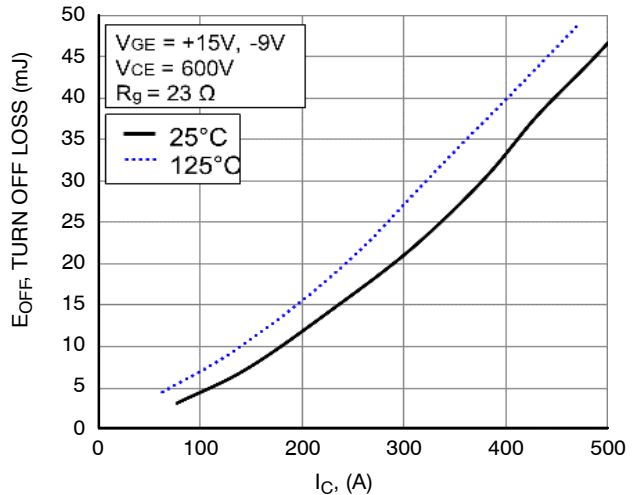


Figure 60. Typical Turn Off Loss vs.  $I_C$

# NXH800A100L4Q2F2S1G/P1G, NXH800A100L4Q2F2S2G/P2G

## TYPICAL CHARACTERISTICS – T2||D3a + D4a or T3||D1a + D2a (continued)

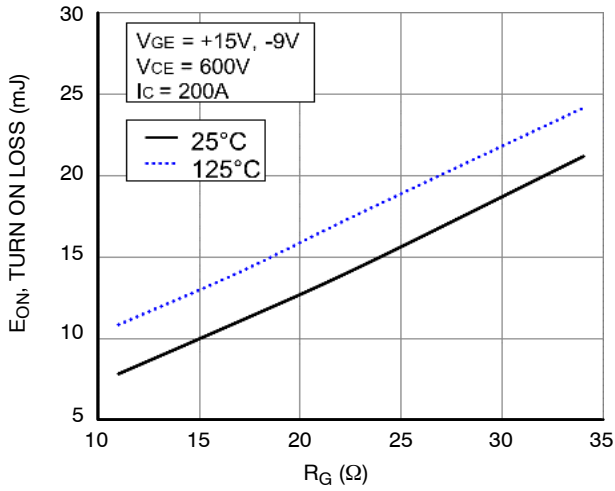


Figure 61. Typical Turn On Loss vs.  $R_G$

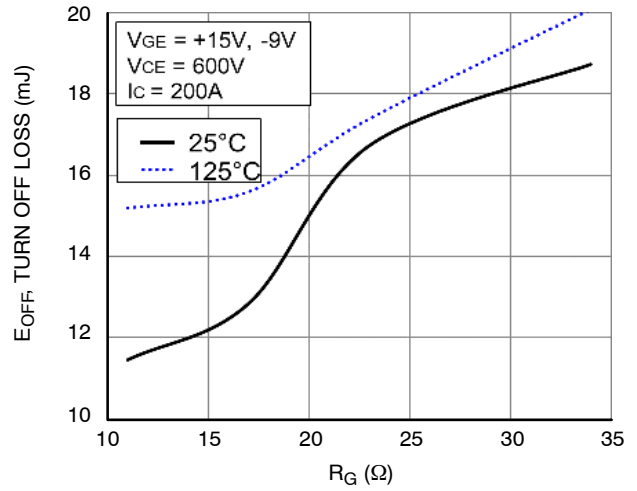


Figure 62. Typical Turn Off Loss vs.  $R_G$

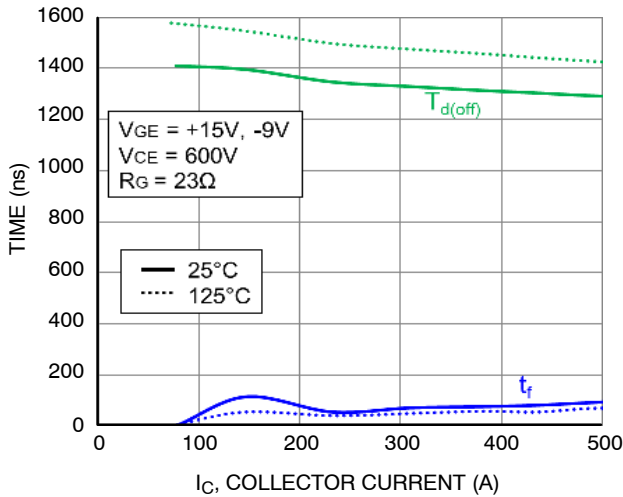


Figure 63. Typical Turn-Off Switching Time vs.  $I_C$

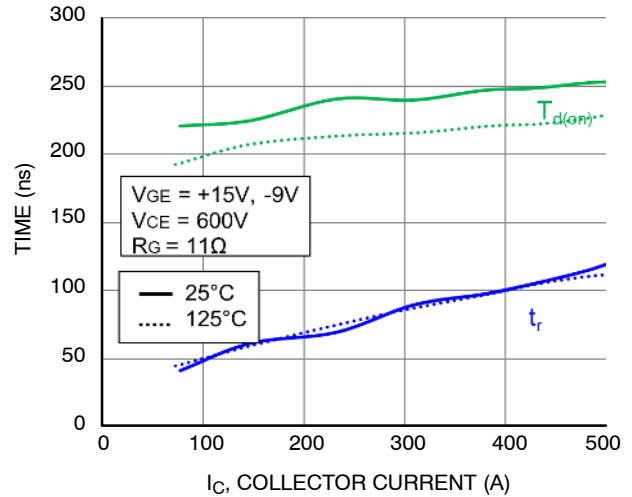


Figure 64. Typical Turn-On Switching Time vs.  $I_C$

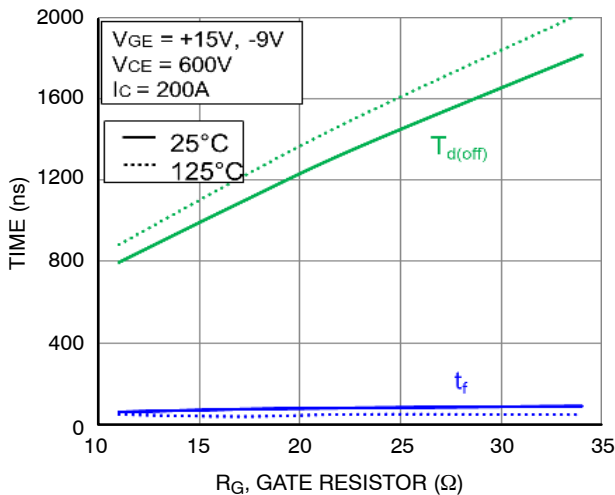


Figure 65. Typical Turn-Off Switching Time vs.  $R_G$

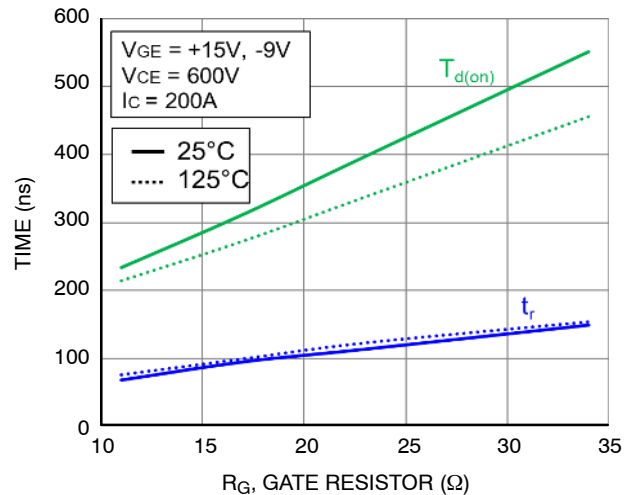


Figure 66. Typical Turn-On Switching Time vs.  $R_G$

# NXH800A100L4Q2F2S1G/P1G, NXH800A100L4Q2F2S2G/P2G

## TYPICAL CHARACTERISTICS – T2||D3a + D4a or T3||D1a + D2a (continued)

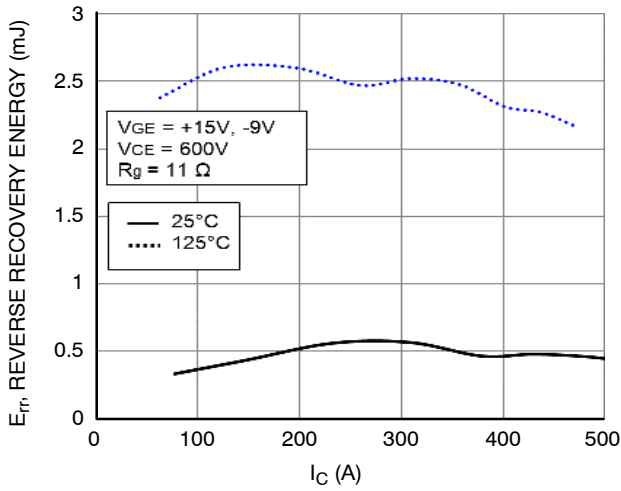


Figure 67. Typical Reverse Recovery Energy Loss vs.  $I_C$

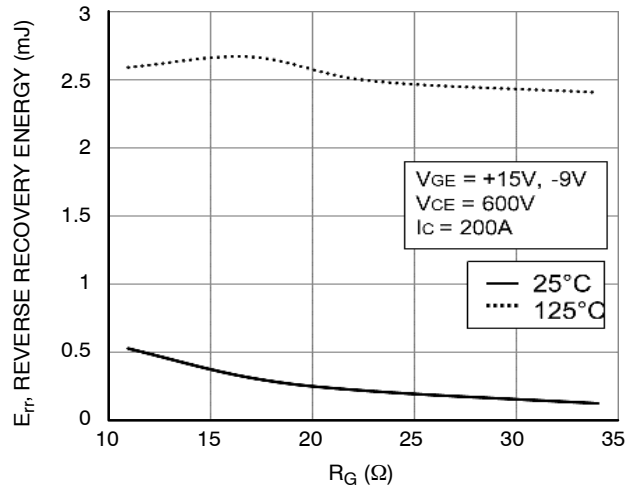


Figure 68. Typical Reverse Recovery Energy Loss vs.  $R_G$

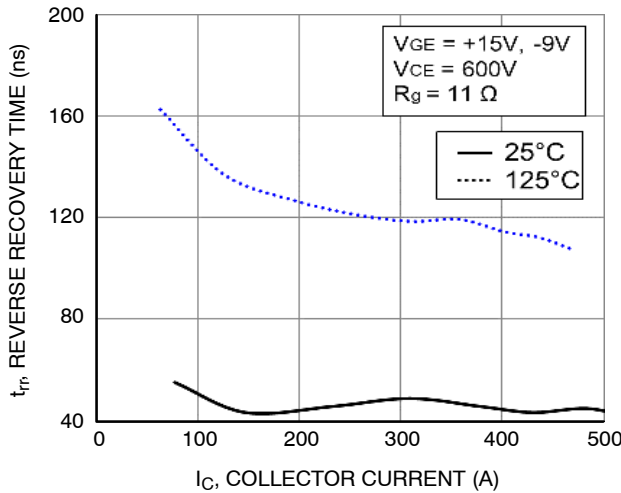


Figure 69. Typical Reverse Recovery Time vs.  $I_C$

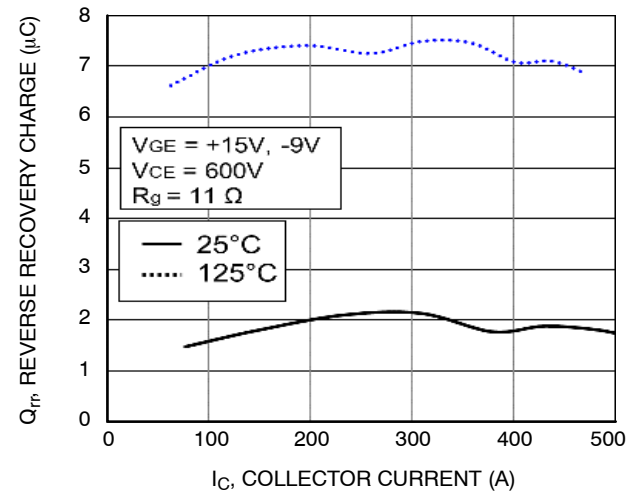


Figure 70. Typical Reverse Recovery Charge vs.  $I_C$

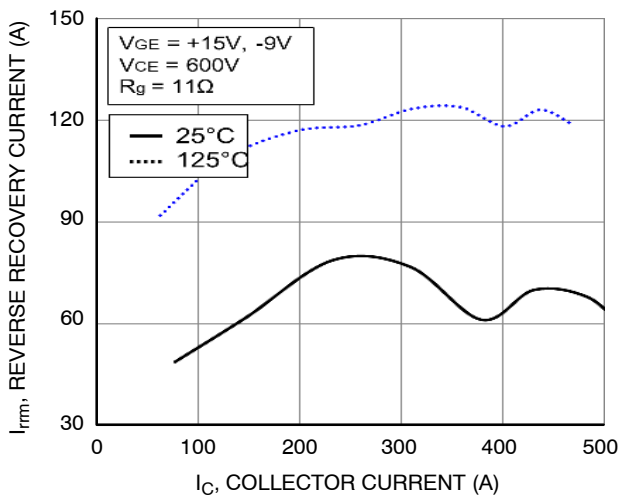


Figure 71. Typical Reverse Recovery Current vs.  $I_C$

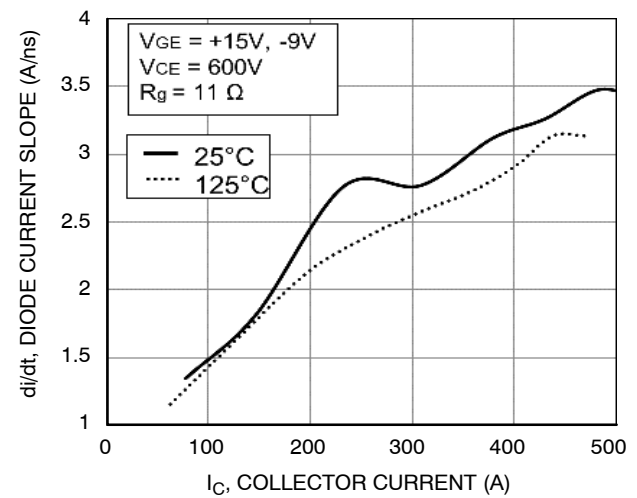


Figure 72. Typical  $di/dt$  vs.  $I_C$

# NXH800A100L4Q2F2S1G/P1G, NXH800A100L4Q2F2S2G/P2G

## TYPICAL CHARACTERISTICS – T2||D3a + D4a or T3||D1a + D2a (continued)

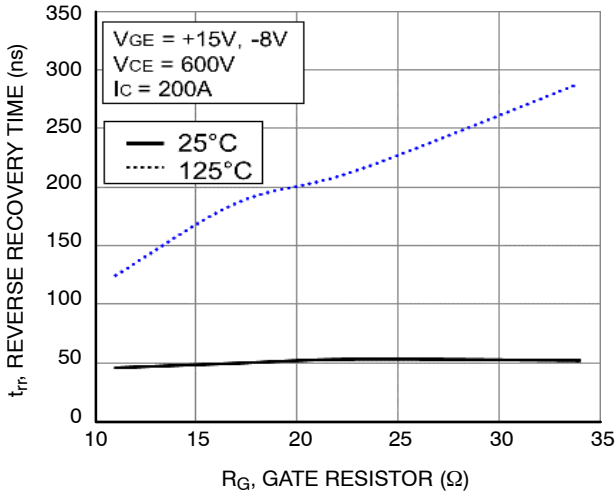


Figure 73. Typical Reverse Recovery Time vs.  $R_G$

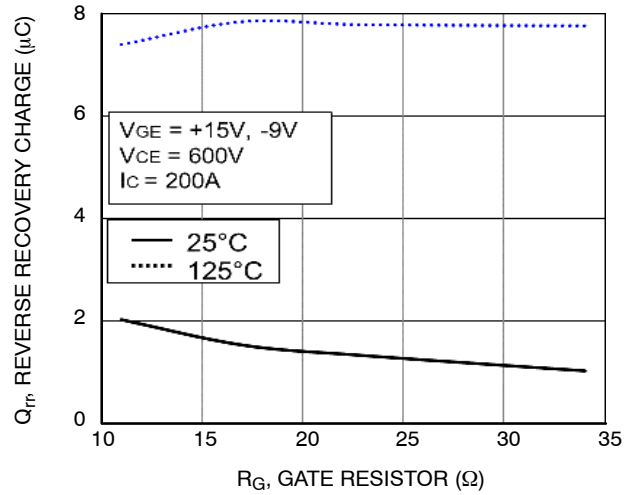


Figure 74. Typical Reverse Recovery Charge vs.  $R_G$

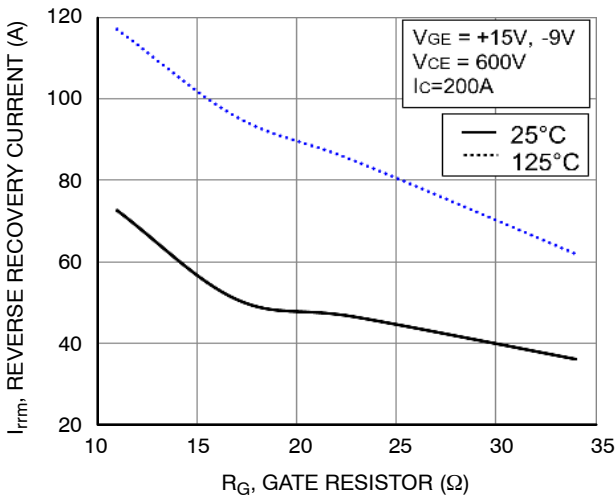


Figure 75. Typical Reverse Recovery Peak Current vs.  $R_G$

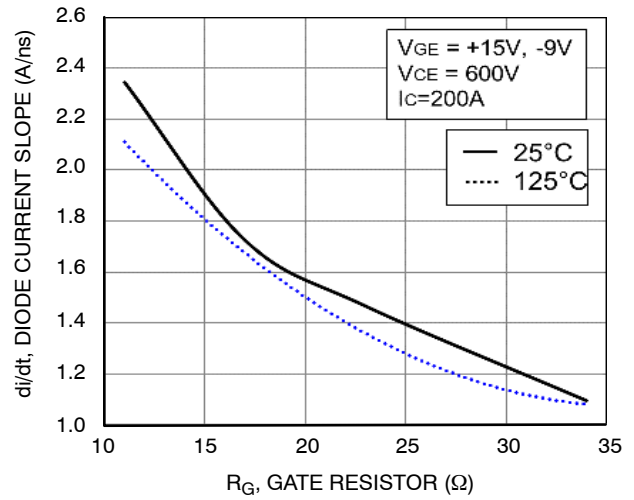


Figure 76. Typical  $di/dt$  vs.  $R_G$

## TYPICAL CHARACTERISTICS – T6||D4a or T5||D1a

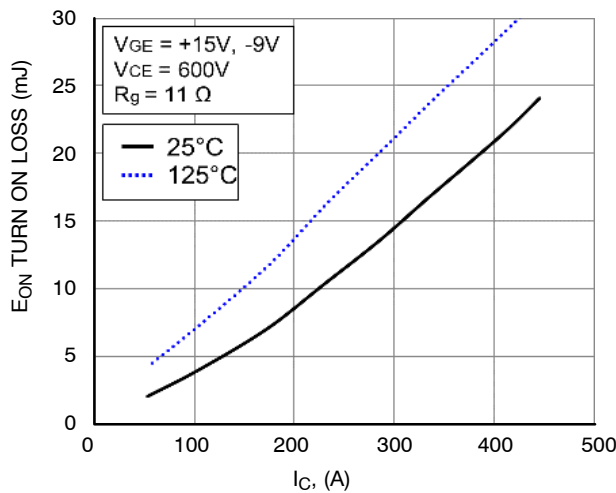


Figure 77. Typical Turn On Loss vs.  $I_C$

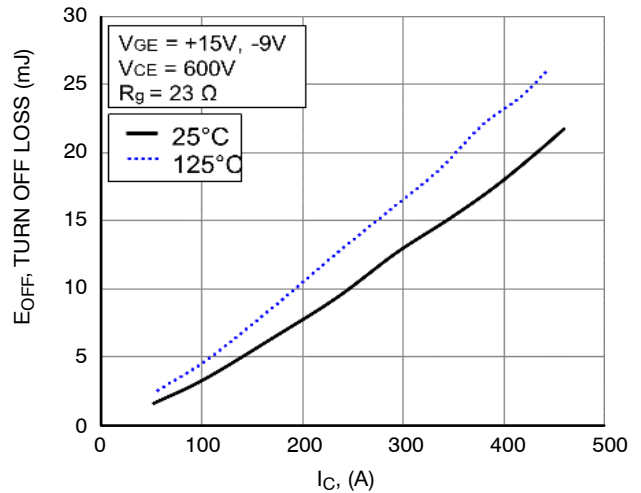


Figure 78. Typical Turn Off Loss vs.  $I_C$

# NXH800A100L4Q2F2S1G/P1G, NXH800A100L4Q2F2S2G/P2G

## TYPICAL CHARACTERISTICS – T6||D4a or T5||D1a (continued)

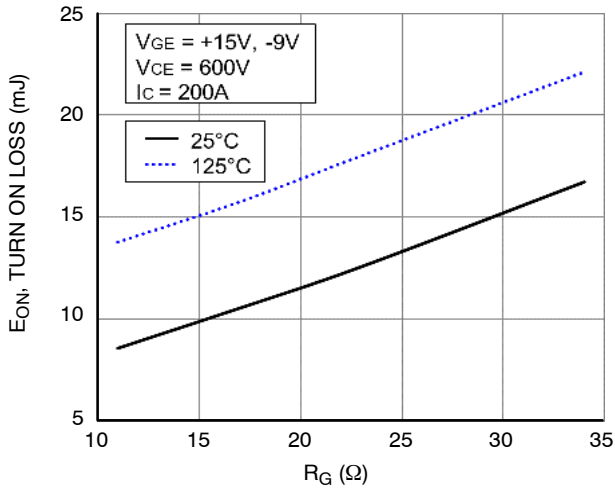


Figure 79. Typical Turn On Loss vs.  $R_G$

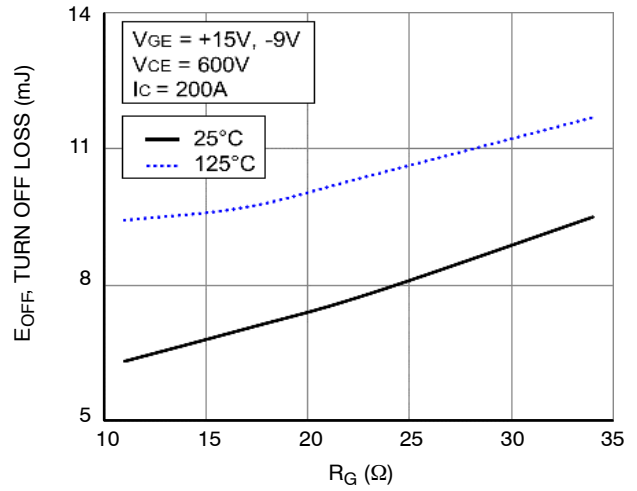


Figure 80. Typical Turn Off Loss vs.  $R_G$

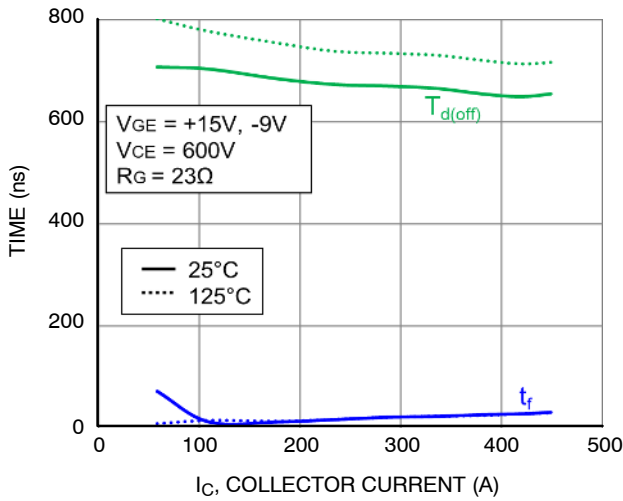


Figure 81. Typical Turn-Off Switching Time vs.  $I_C$

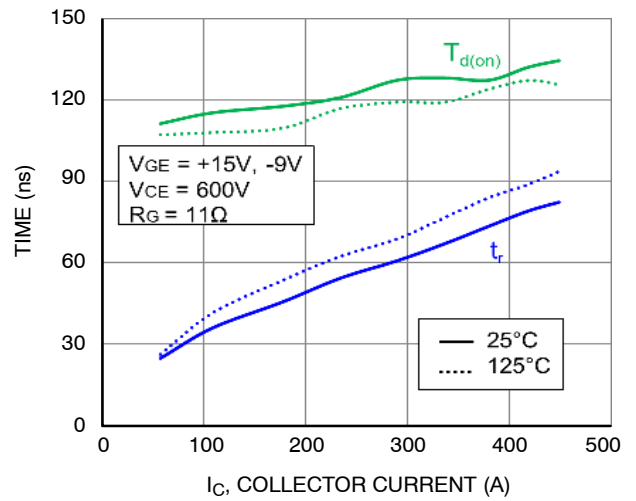


Figure 82. Typical Turn-On Switching Time vs.  $I_C$

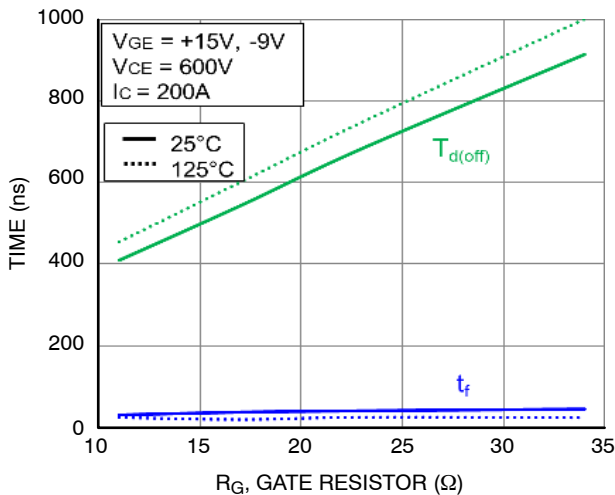


Figure 83. Typical Turn-Off Switching Time vs.  $R_G$

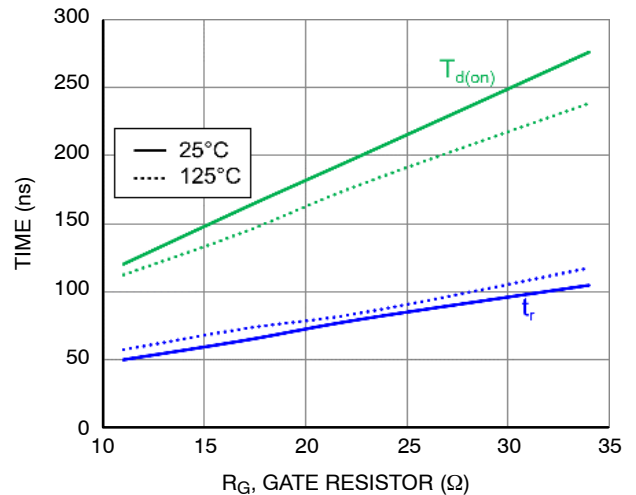


Figure 84. Typical Turn-On Switching Time vs.  $R_G$

# NXH800A100L4Q2F2S1G/P1G, NXH800A100L4Q2F2S2G/P2G

## TYPICAL CHARACTERISTICS – T6||D4a or T5||D1a (continued)

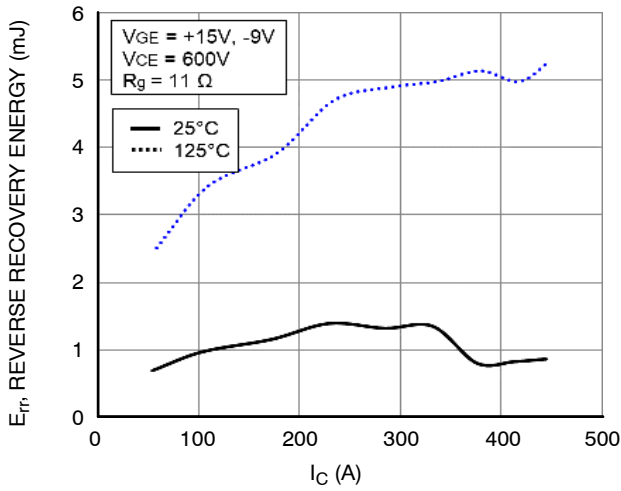


Figure 85. Typical Reverse Recovery Energy Loss vs.  $I_C$

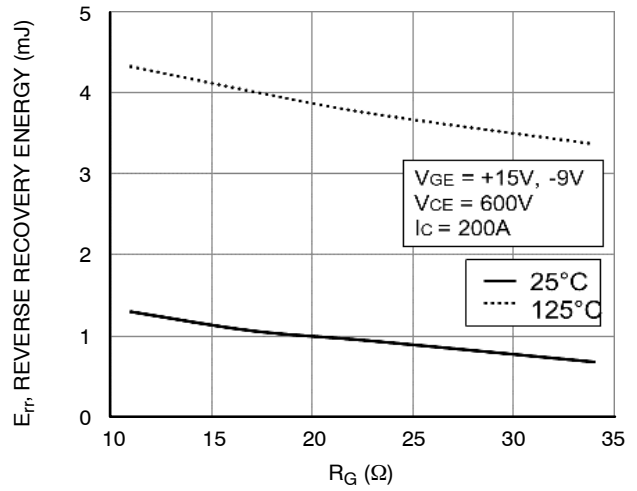


Figure 86. Typical Reverse Recovery Energy Loss vs.  $R_G$

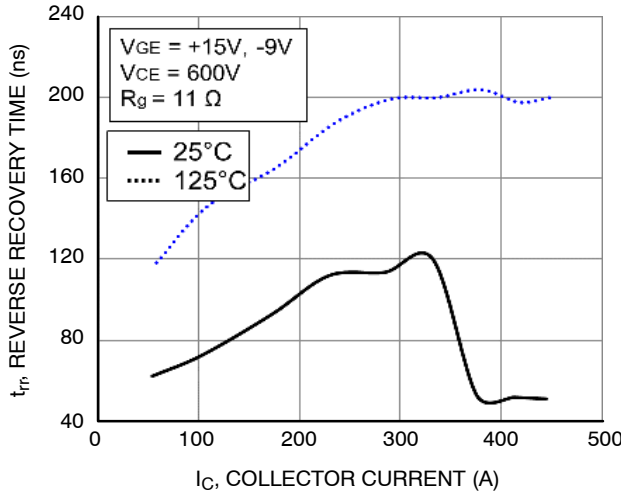


Figure 87. Typical Reverse Recovery Time vs.  $I_C$

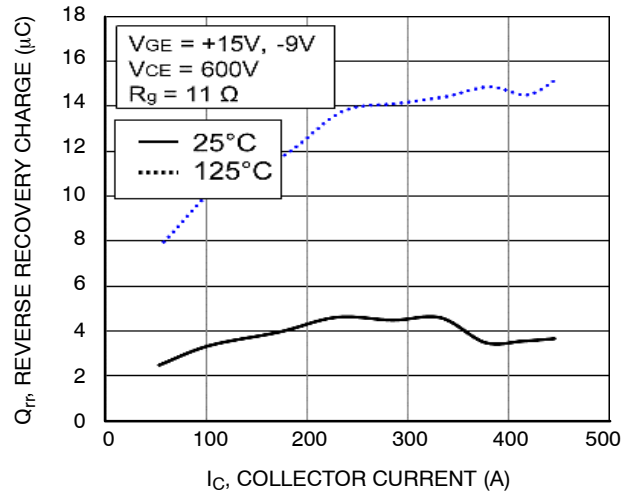


Figure 88. Typical Reverse Recovery Charge vs.  $I_C$

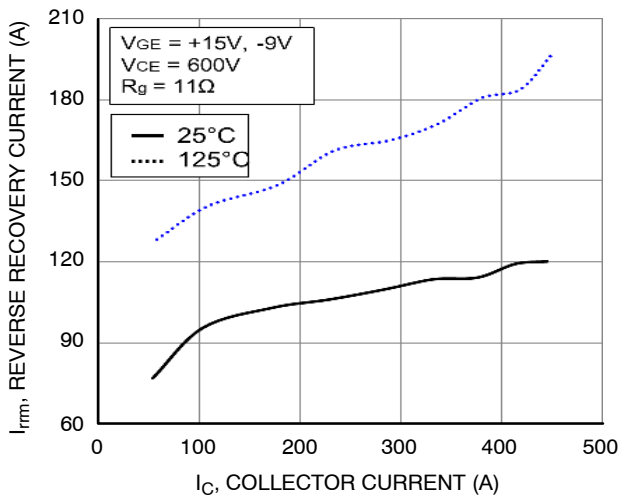


Figure 89. Typical Reverse Recovery Current vs.  $I_C$

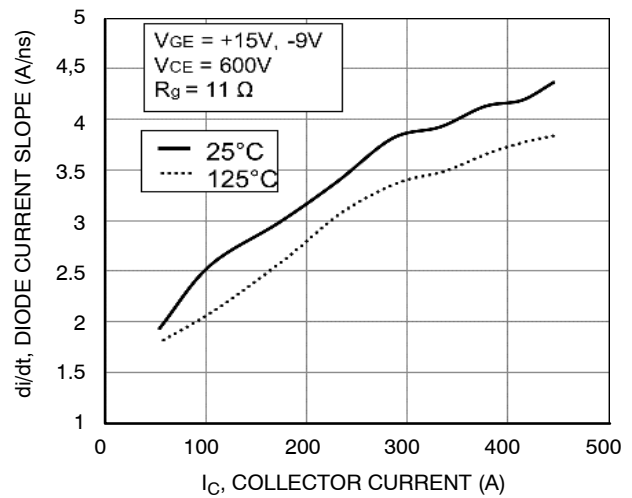


Figure 90. Typical  $di/dt$  vs.  $I_C$



# NXH800A100L4Q2F2S1G/P1G, NXH800A100L4Q2F2S2G/P2G

## TYPICAL CHARACTERISTICS – T6||D4a or T5||D1a (continued)

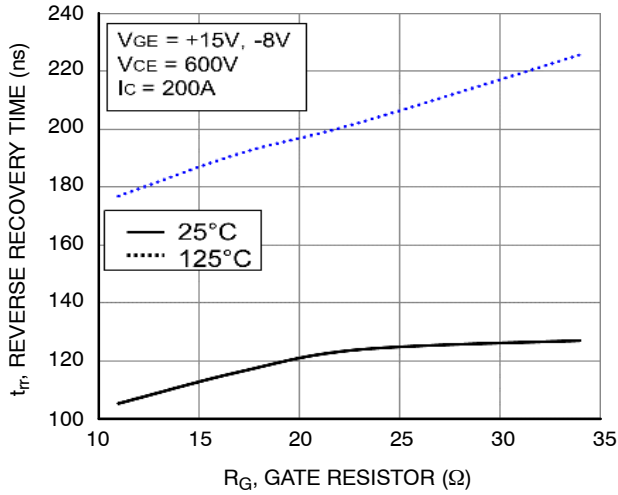


Figure 91. Typical Reverse Recovery Time vs.  $R_G$

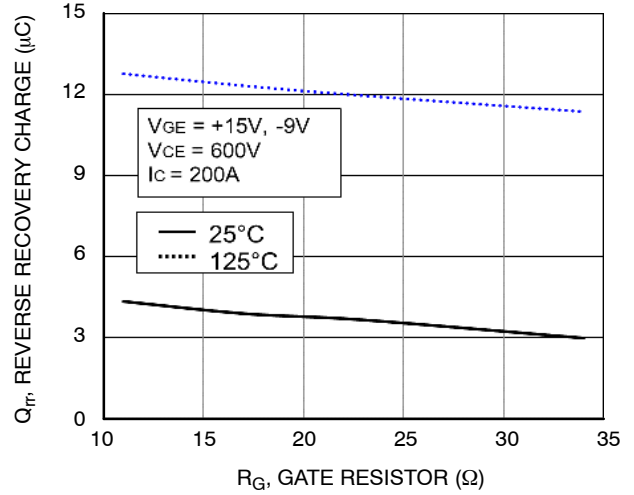


Figure 92. Typical Reverse Recovery Charge vs.  $R_G$

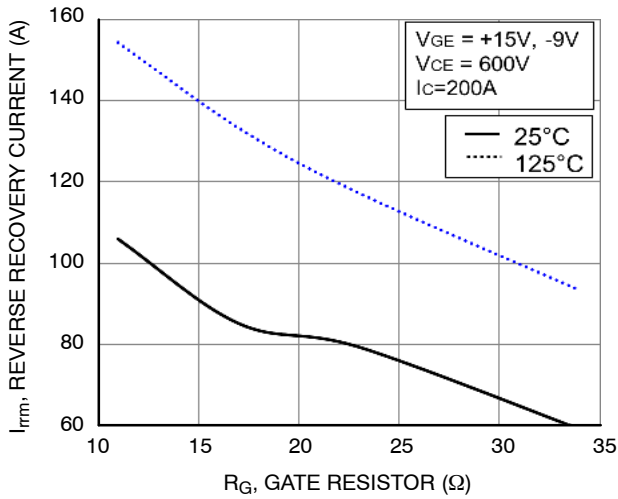


Figure 93. Typical Reverse Recovery Peak Current vs.  $R_G$

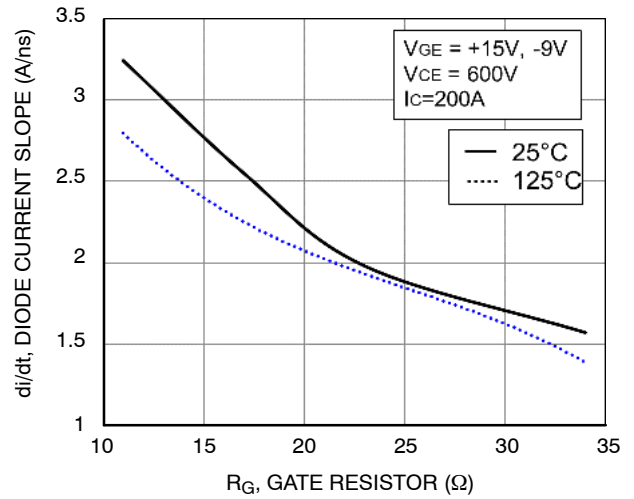
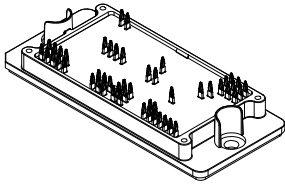
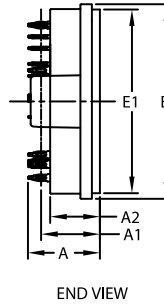
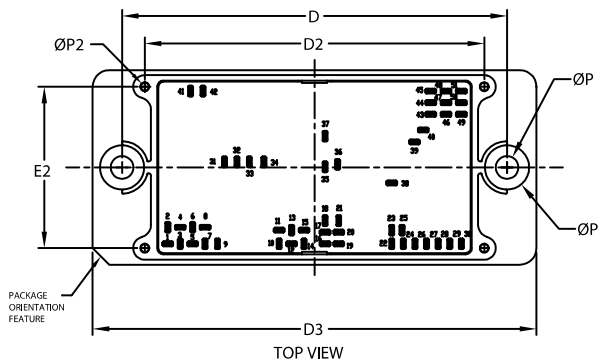
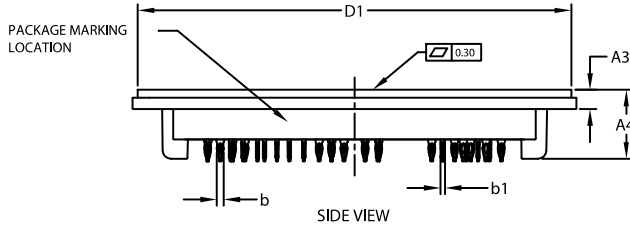


Figure 94. Typical  $di/dt$  vs.  $R_G$

# NXH800A100L4Q2F2S1G/P1G, NXH800A100L4Q2F2S2G/P2G



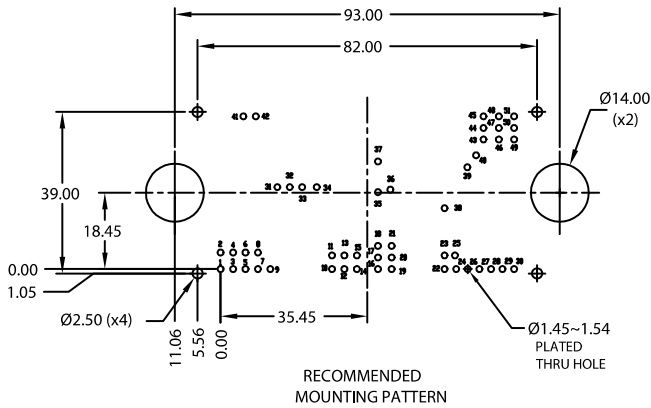
## PIM51, 93x47 (PRESS FIT) CASE 180HG ISSUE O



**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009
2. CONTROLLING DIMENSION : MILLIMETERS
3. DIMENSIONS b AND b1 APPLY TO THE PLATED TERMINALS AND ARE MEASURED AT DIMENSION A1
4. PIN POSITION TOLERANCE IS ± 0.4mm
5. PACKAGE MARKING IS LOCATED AS SHOWN ON THE SIDE OPPOSITE THE PACKAGE ORIENTATION FEATURES

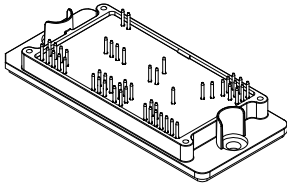
DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	16.90	17.30	17.70
A1	14.18(REF)		
A2	11.70	12.00	12.30
A3	4.40	4.70	5.00
A4	16.40	16.70	17.00
b	1.61	1.66	1.71
b1	0.75	0.80	0.85
D	92.90	93.00	93.10
D1	104.45	104.75	105.05
D2	81.80	82.00	82.20
D3	106.90	107.20	107.50
E	46.70	47.00	47.30
E1	44.10	44.40	44.70
E2	38.80	39.00	39.20
P	5.40	5.50	5.60
P1	10.60	10.70	10.80
P2	1.80	2.00	2.20



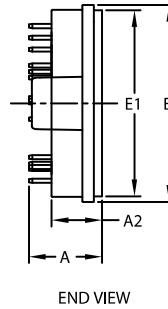
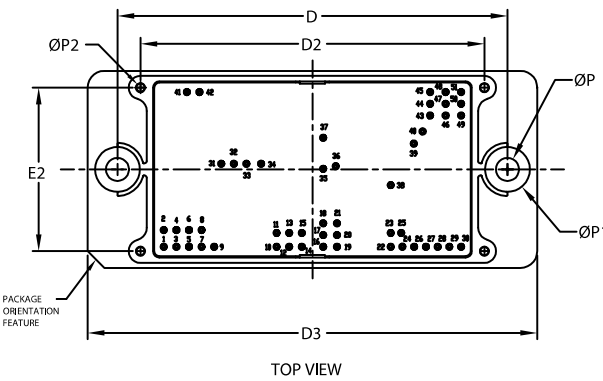
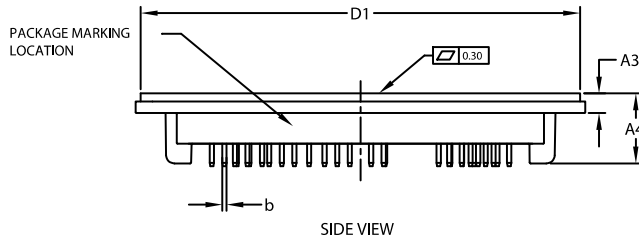
**NOTE 4**

PIN	PIN POSITION		PIN	PIN POSITION	
	X	Y		X	Y
1	0.00	0.00	27	62.50	0.00
2	0.00	4.00	28	65.30	0.00
3	3.00	0.00	29	68.10	0.00
4	3.00	4.00	30	70.90	0.00
5	6.00	0.00	31	13.70	19.80
6	6.00	4.00	32	16.70	19.80
7	9.00	0.00	33	19.70	19.80
8	9.00	4.00	34	23.20	19.80
9	12.00	0.00	35	38.00	18.60
10	26.90	0.00	36	41.00	19.20
11	26.90	3.30	37	38.00	26.00
12	29.90	0.00	38	54.10	14.70
13	29.90	3.30	39	59.60	24.60
14	32.90	0.00	40	61.70	27.50
15	32.90	3.30	41	5.50	36.90
16	38.00	0.00	42	8.50	36.90
17	38.00	2.80	43	63.50	31.30
18	38.00	5.60	44	63.50	34.10
19	41.30	0.00	45	63.50	36.90
20	41.30	2.80	46	67.20	31.30
21	41.30	5.60	47	67.20	34.10
22	54.10	0.00	48	67.20	36.90
23	54.10	3.30	49	70.90	31.30
24	56.90	0.00	50	70.90	34.10
25	56.60	3.30	51	70.90	36.90
26	59.70	0.00			

# NXH800A100L4Q2F2S1G/P1G, NXH800A100L4Q2F2S2G/P2G



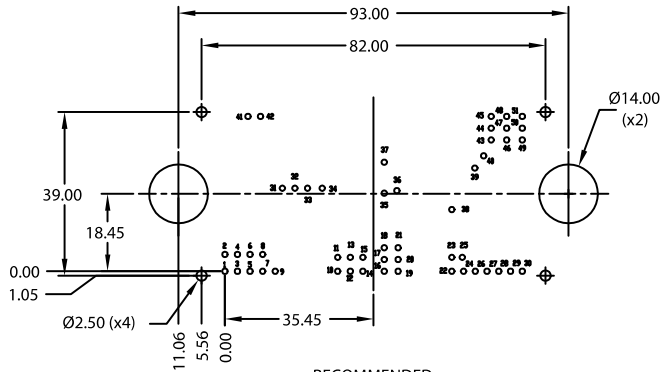
## PIM51, 93x47 (SOLDER PIN) CASE 180HH ISSUE O



**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009
2. CONTROLLING DIMENSION : MILLIMETERS
3. DIMENSIONS b AND b1 APPLY TO THE PLATED TERMINALS AND ARE MEASURED AT DIMENSION A1
4. PIN POSITION TOLERANCE IS  $\pm 0.4\text{mm}$
5. PACKAGE MARKING IS LOCATED AS SHOWN ON THE SIDE OPPOSITE THE PACKAGE ORIENTATION FEATURES

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	17.00	17.40	17.80
A2	11.70	12.00	12.30
A3	4.40	4.70	5.00
A4	16.40	16.70	17.00
b	0.95	1.00	1.05
D	92.90	93.00	93.10
D1	104.45	104.75	105.05
D2	81.80	82.00	82.20
D3	106.90	107.20	107.50
E	46.70	47.00	47.30
E1	44.10	44.40	44.70
E2	38.80	39.00	39.20
P	5.40	5.50	5.60
P1	10.60	10.70	10.80
P2	1.80	2.00	2.20

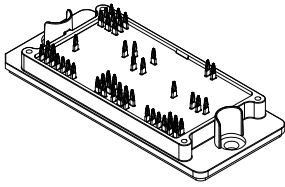


\* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

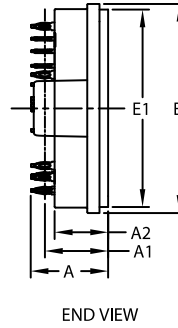
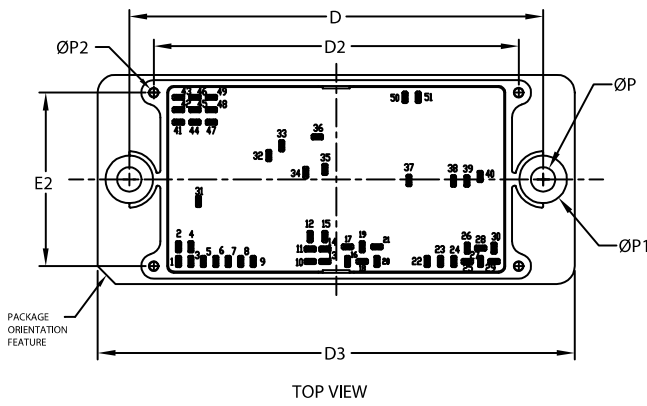
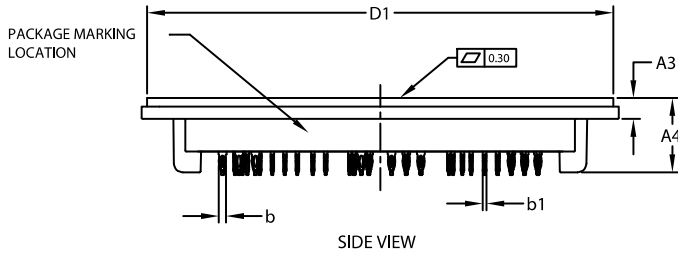
**NOTE 4**

PIN	PIN POSITION		PIN	PIN POSITION	
	X	Y		X	Y
1	0.00	0.00	27	62.50	0.00
2	0.00	4.00	28	65.30	0.00
3	3.00	0.00	29	68.10	0.00
4	3.00	4.00	30	70.90	0.00
5	6.00	0.00	31	13.70	19.80
6	6.00	4.00	32	16.70	19.80
7	9.00	0.00	33	19.70	19.80
8	9.00	4.00	34	23.20	19.80
9	12.00	0.00	35	38.00	18.60
10	26.90	0.00	36	41.00	19.20
11	26.90	3.30	37	38.00	26.00
12	29.90	0.00	38	54.10	14.70
13	29.90	3.30	39	59.60	24.60
14	32.90	0.00	40	61.70	27.50
15	32.90	3.30	41	5.50	36.90
16	38.00	0.00	42	8.50	36.90
17	38.00	2.80	43	63.50	31.30
18	38.00	5.60	44	63.50	34.10
19	41.30	0.00	45	63.50	36.90
20	41.30	2.80	46	67.20	31.30
21	41.30	5.60	47	67.20	34.10
22	54.10	0.00	48	67.20	36.90
23	54.10	3.30	49	70.90	31.30
24	56.90	0.00	50	70.90	34.10
25	56.60	3.30	51	70.90	36.90
26	59.70	0.00			

# NXH800A100L4Q2F2S1G/P1G, NXH800A100L4Q2F2S2G/P2G



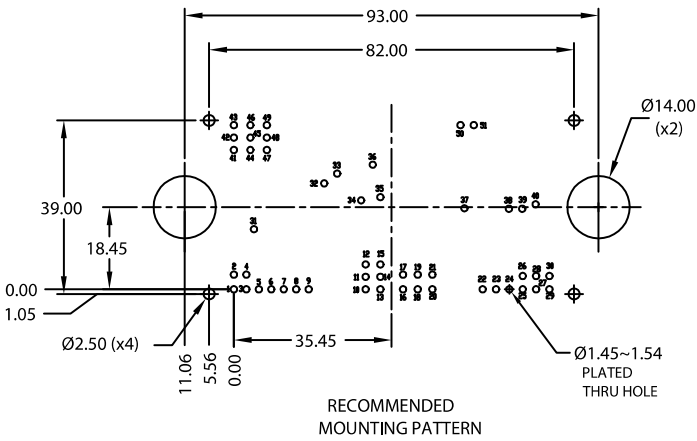
## PIM51, 93x47 (PRESS FIT) CASE 180CQ ISSUE O



**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS b AND b1 APPLY TO THE PLATED TERMINALS AND ARE MEASURED AT DIMENSION A1
4. PIN POSITION TOLERANCE IS  $\pm 0.4\text{mm}$
5. PACKAGE MARKING IS LOCATED AS SHOWN ON THE SIDE OPPOSITE THE PACKAGE ORIENTATION FEATURES

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	16.90	17.30	17.70
A1	14.18(REF)		
A2	11.70	12.00	12.30
A3	4.40	4.70	5.00
A4	16.40	16.70	17.00
b	1.61	1.66	1.71
b1	0.75	0.80	0.85
D	92.90	93.00	93.10
D1	104.45	104.75	105.05
D2	81.80	82.00	82.20
D3	106.90	107.20	107.50
E	46.70	47.00	47.30
E1	44.10	44.40	44.70
E2	38.80	39.00	39.20
P	5.40	5.50	5.60
P1	10.60	10.70	10.80
P2	1.80	2.00	2.20

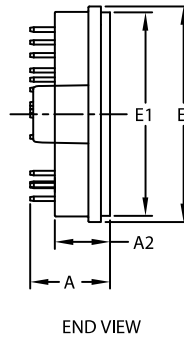
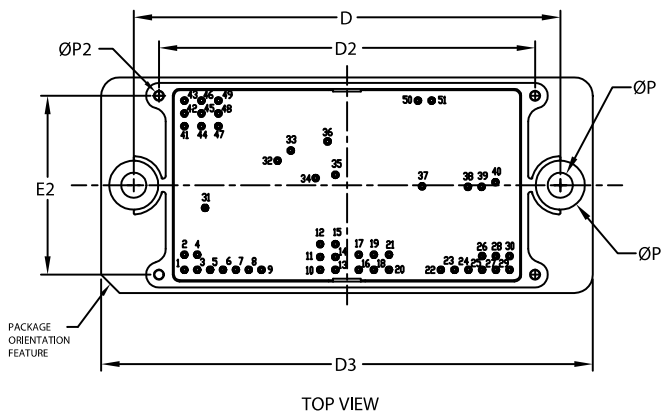
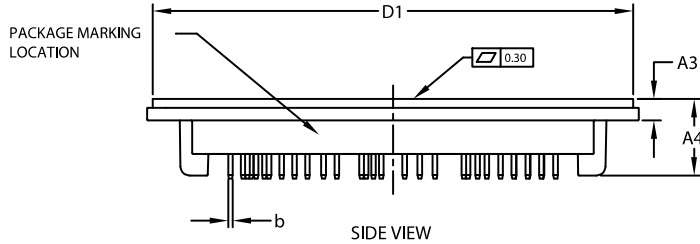
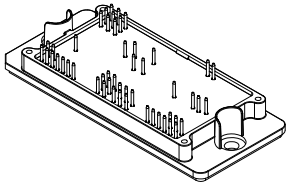


**NOTE 4**

PIN	PIN POSITION		PIN	PIN POSITION	
	X	Y		X	Y
1	0.00	0.00	27	67.90	0.00
2	0.00	3.30	28	67.90	3.00
3	2.80	0.00	29	70.90	0.00
4	2.80	3.30	30	70.90	3.00
5	5.60	0.00	31	4.50	13.50
6	8.40	0.00	32	20.30	23.80
7	11.20	0.00	33	23.20	26.00
8	14.00	0.00	34	28.60	20.00
9	16.80	0.00	35	32.90	20.70
10	29.60	0.00	36	31.20	28.00
11	29.60	2.80	37	51.80	18.20
12	29.60	5.60	38	61.80	18.10
13	32.90	0.00	39	64.80	18.10
14	32.90	2.80	40	67.80	19.10
15	32.90	5.60	41	0.00	31.30
16	38.00	0.00	42	0.00	34.10
17	38.00	3.30	43	0.00	36.90
18	41.30	0.00	44	3.70	31.30
19	41.30	3.30	45	3.70	34.10
20	44.60	0.00	46	3.70	36.90
21	44.60	3.30	47	7.40	31.30
22	55.90	0.00	48	7.40	34.10
23	58.90	0.00	49	7.40	36.90
24	61.90	0.00	50	59.90	36.90
25	64.90	0.00	51	53.90	36.90
26	64.90	3.00			

# NXH800A100L4Q2F2S1G/P1G, NXH800A100L4Q2F2S2G/P2G

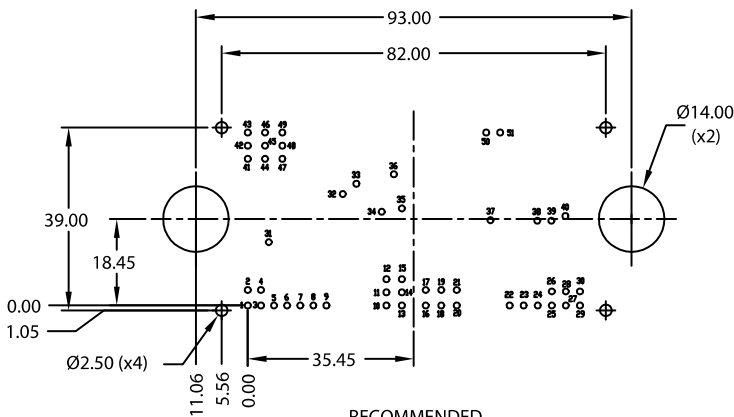
## PIM51, 93x47 (SOLDER PIN) CASE 180BM ISSUE O



**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009
2. CONTROLLING DIMENSION : MILLIMETERS
3. DIMENSIONS b AND b1 APPLY TO THE PLATED TERMINALS AND ARE MEASURED AT DIMENSION A1
4. PIN POSITION TOLERANCE IS  $\pm 0.4\text{mm}$
5. PACKAGE MARKING IS LOCATED AS SHOWN ON THE SIDE OPPOSITE THE PACKAGE ORIENTATION FEATURES

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	17.00	17.40	17.80
A2	11.70	12.00	12.30
A3	4.40	4.70	5.00
A4	16.40	16.70	17.00
b	0.95	1.00	1.05
D	92.90	93.00	93.10
D1	104.45	104.75	105.05
D2	81.80	82.00	82.20
D3	106.90	107.20	107.50
E	46.70	47.00	47.30
E1	44.10	44.40	44.70
E2	38.80	39.00	39.20
P	5.40	5.50	5.60
P1	10.60	10.70	10.80
P2	1.80	2.00	2.20



\* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

**NOTE 4**

PIN	PIN POSITION		PIN	PIN POSITION	
	X	Y		X	Y
1	0.00	0.00	27	67.90	0.00
2	0.00	3.30	28	67.90	3.00
3	2.80	0.00	29	70.90	0.00
4	2.80	3.30	30	70.90	3.00
5	5.60	0.00	31	4.50	13.50
6	8.40	0.00	32	20.30	23.80
7	11.20	0.00	33	23.20	26.00
8	14.00	0.00	34	28.60	20.00
9	16.80	0.00	35	32.90	20.70
10	29.60	0.00	36	31.20	28.00
11	29.60	2.80	37	51.80	18.20
12	29.60	5.60	38	61.80	18.10
13	32.90	0.00	39	64.80	18.10
14	32.90	2.80	40	67.80	19.10
15	32.90	5.60	41	0.00	31.30
16	38.00	0.00	42	0.00	34.10
17	38.00	3.30	43	0.00	36.90
18	41.30	0.00	44	3.70	31.30
19	41.30	3.30	45	3.70	34.10
20	44.60	0.00	46	3.70	36.90
21	44.60	3.30	47	7.40	31.30
22	55.90	0.00	48	7.40	34.10
23	58.90	0.00	49	7.40	36.90
24	61.90	0.00	50	50.90	36.90
25	64.90	0.00	51	53.90	36.90
26	64.90	3.00			

# NXH800A100L4Q2F2S1G/P1G, NXH800A100L4Q2F2S2G/P2G

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